

$$V_i(t) = V_m \sin(\omega t), \omega = 2\pi f = 2\pi/T$$

Kapasitör yok ise ortalama DC gerilim
Yarım Dalga Doğrultucu işi

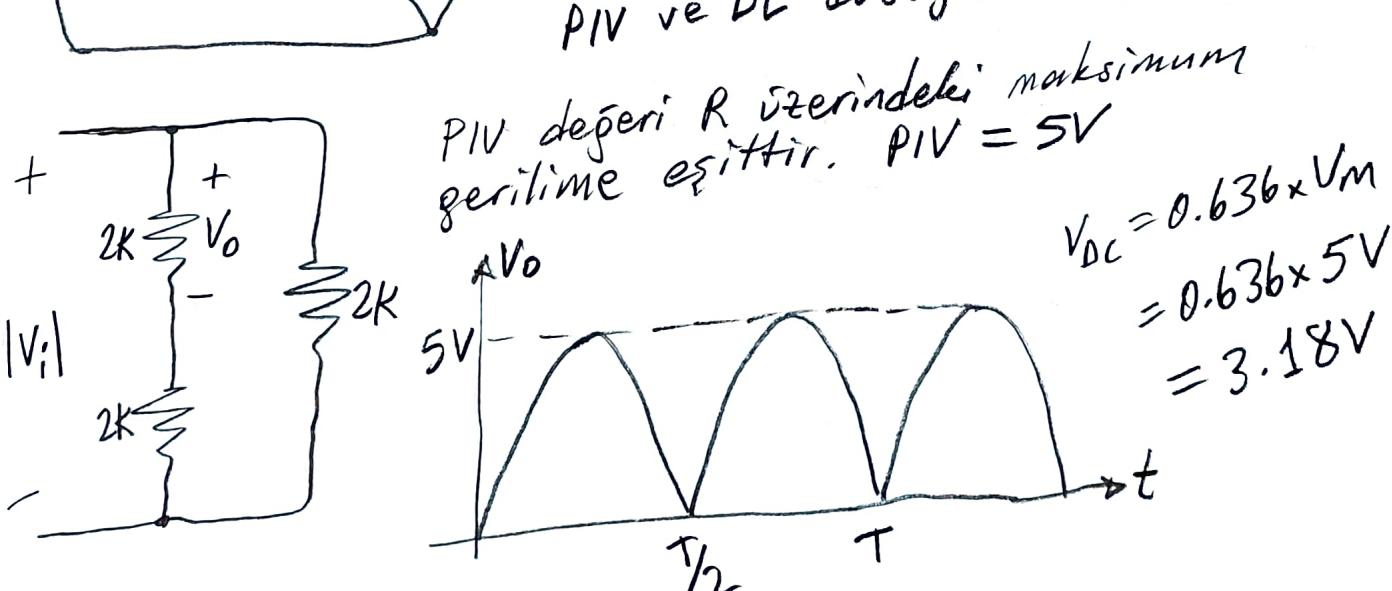
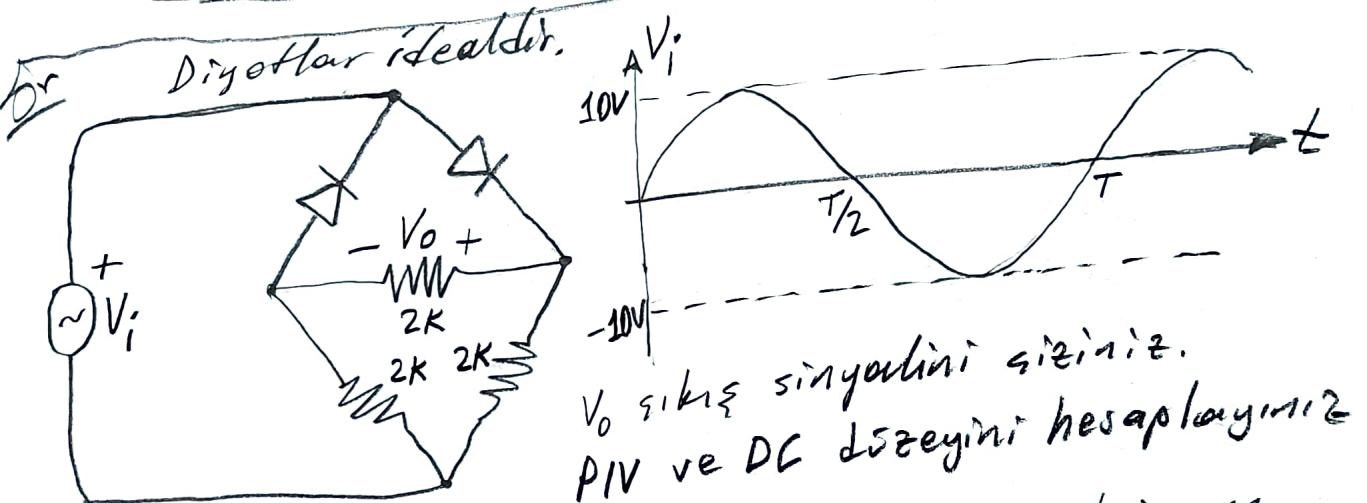
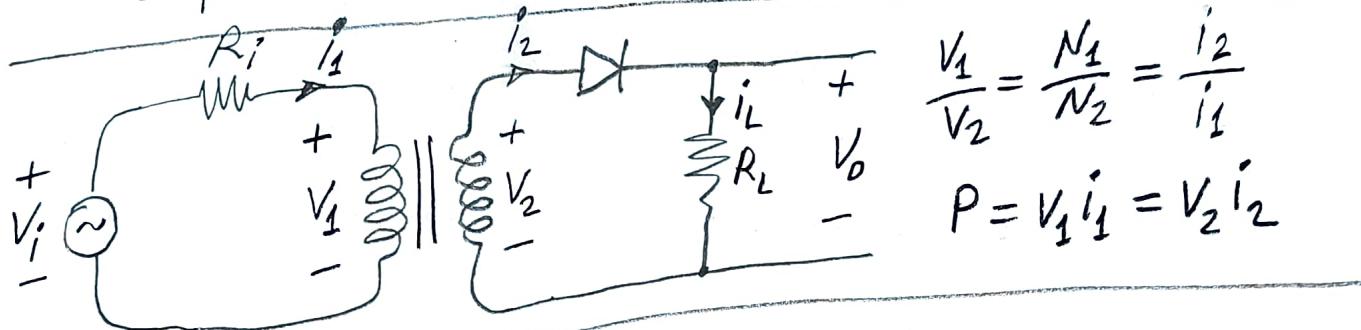
$$V_{DC} \approx \frac{V_m - V_T}{\pi} \approx 0.318 (V_m - V_T)$$

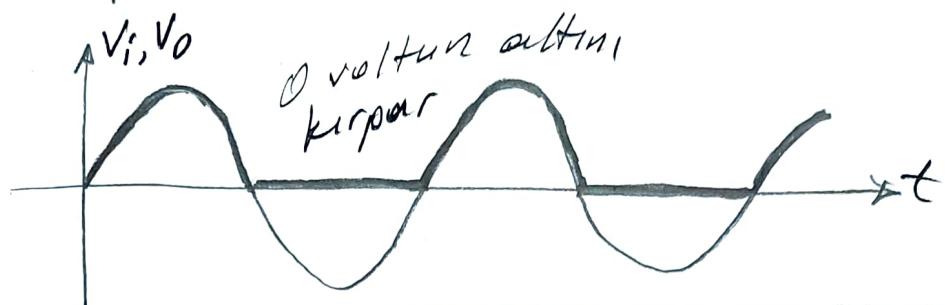
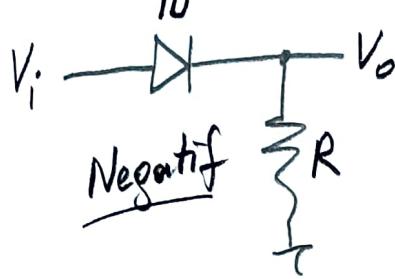
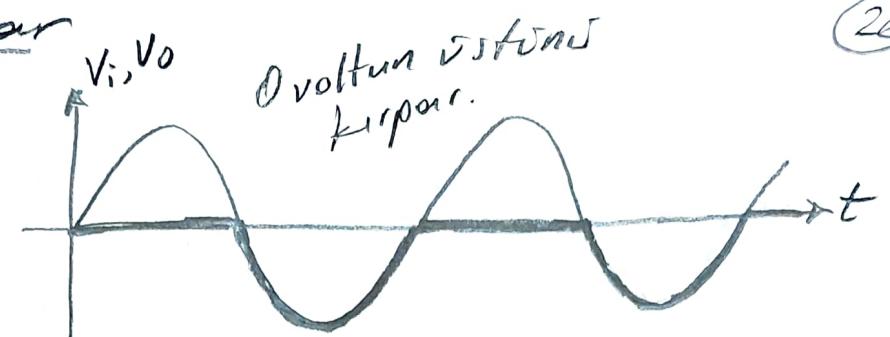
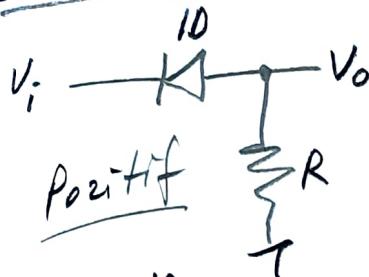
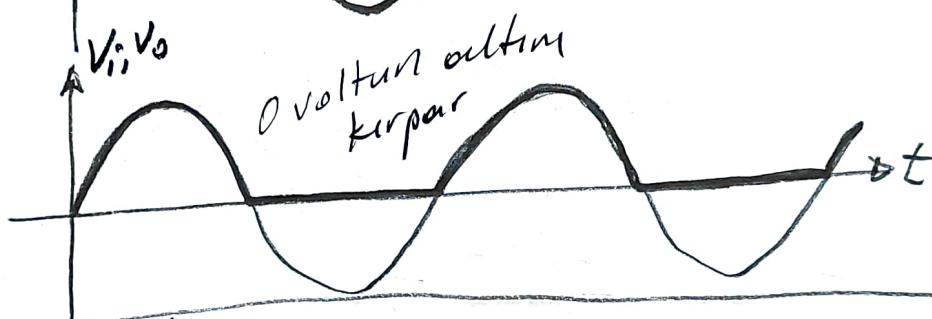
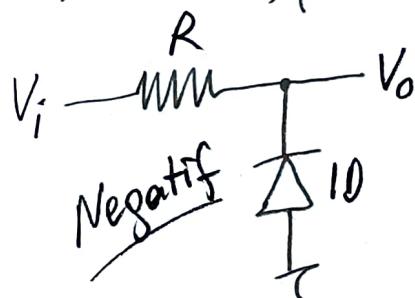
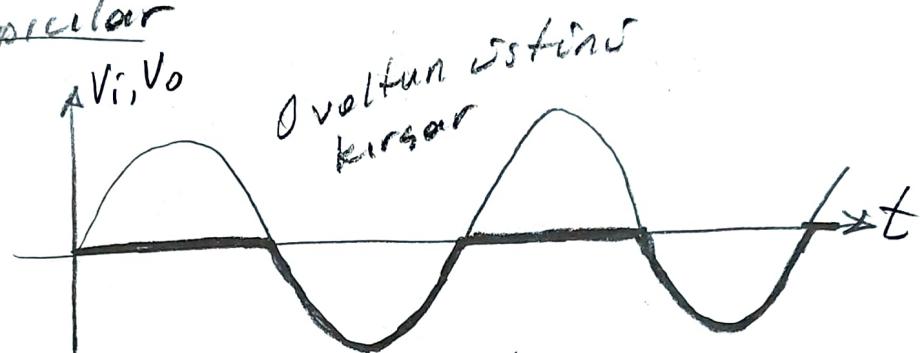
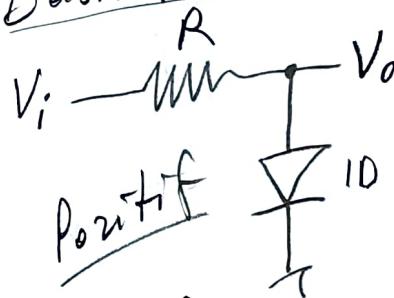
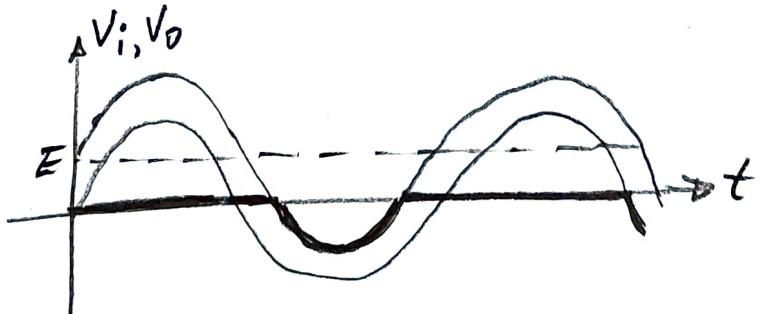
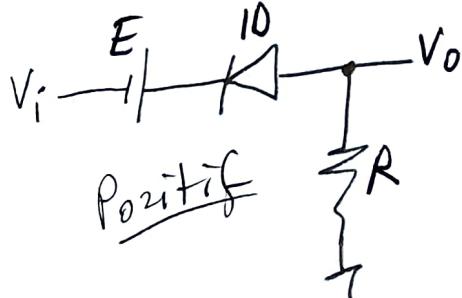
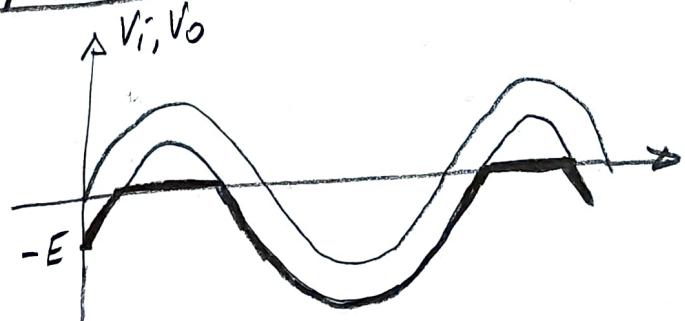
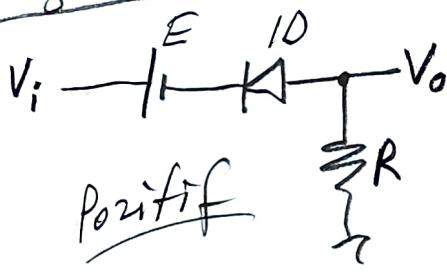
$$V_T = 0.7V \ll V_m \text{ ise } V_{DC} \approx 0.318 V_m$$

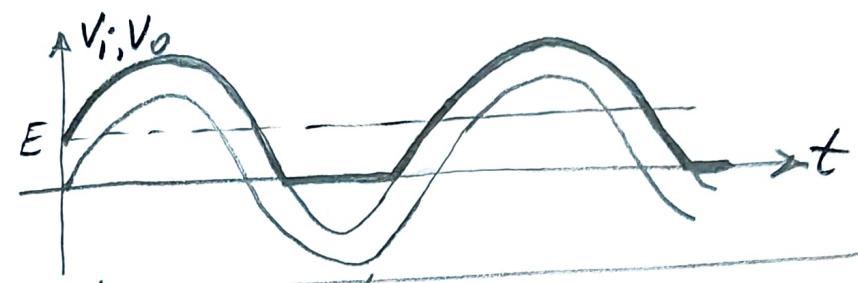
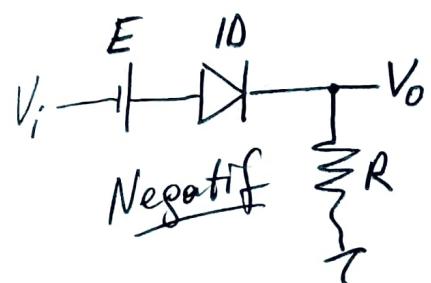
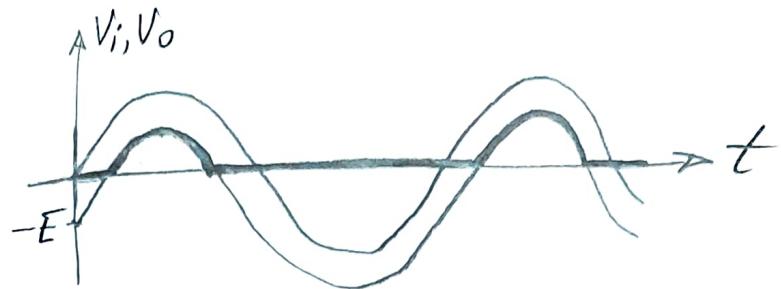
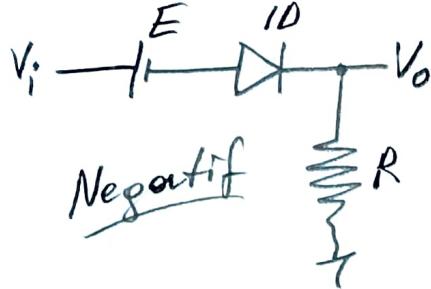
Tam Dalga Doğrultucu işi

$$V_{DC} \approx \frac{V_m - 2V_T}{\pi/2} \approx 0.636 (V_m - 2V_T)$$

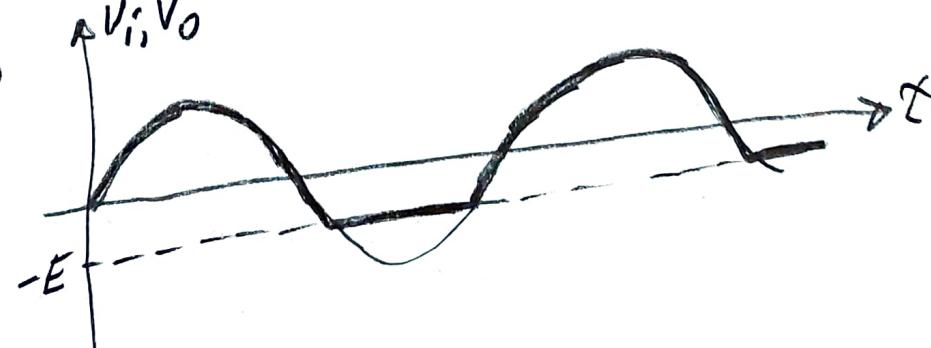
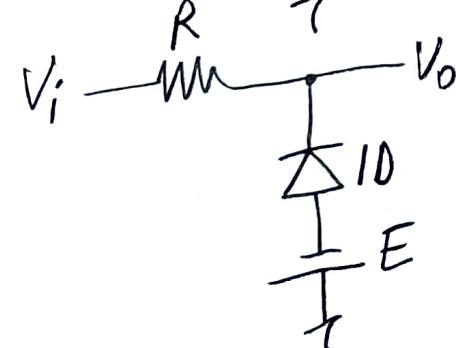
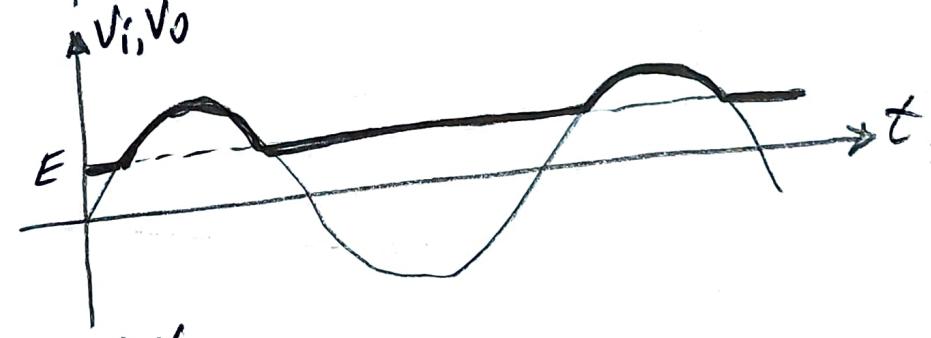
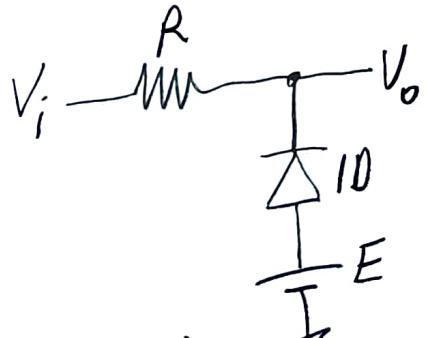
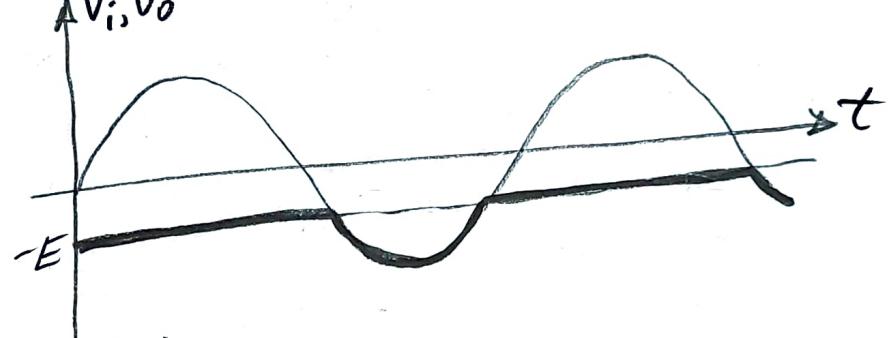
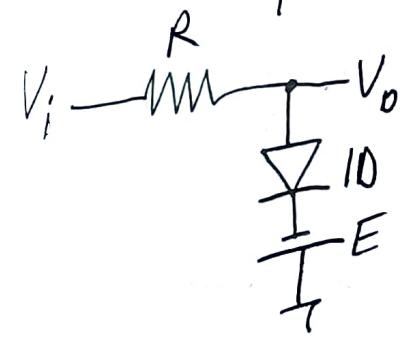
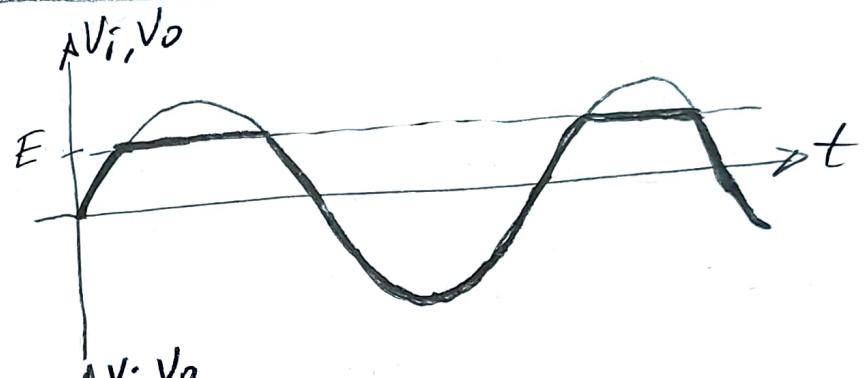
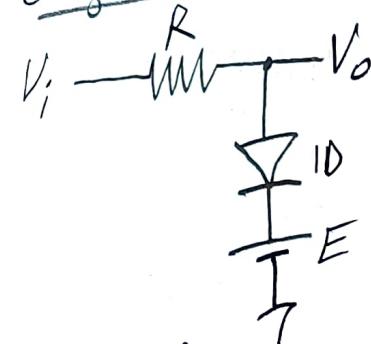
$$2V_T = 1.4V \ll V_m \text{ ise } V_{DC} \approx 0.636 V_m$$

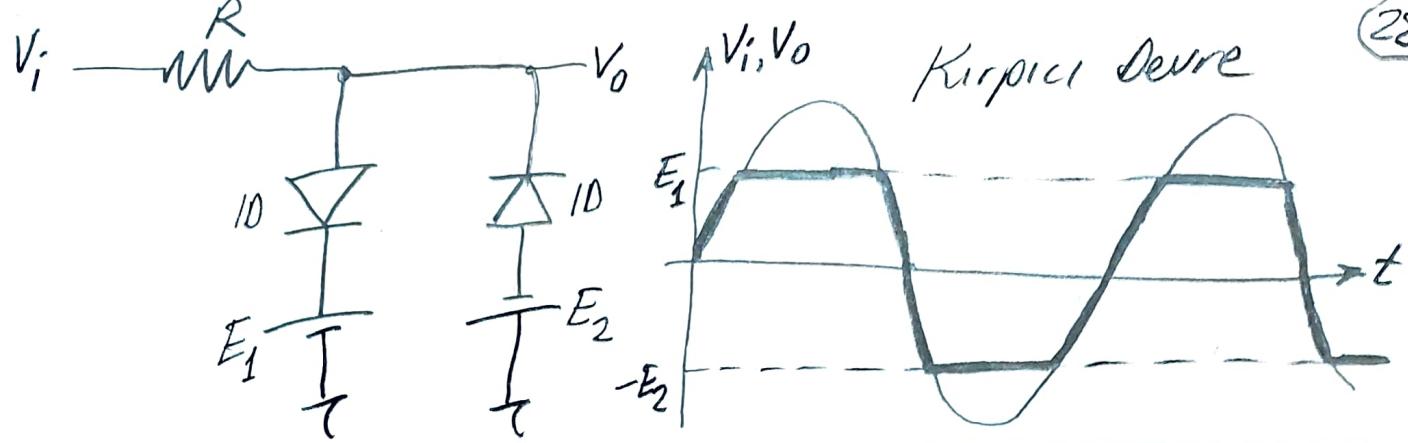


Basit Seri KırıçıcılarBasit Paralel KırıçıcılarÖngeritimi Seri Kırıçıcılar



Ongerilimli Parallel Kırımcılar



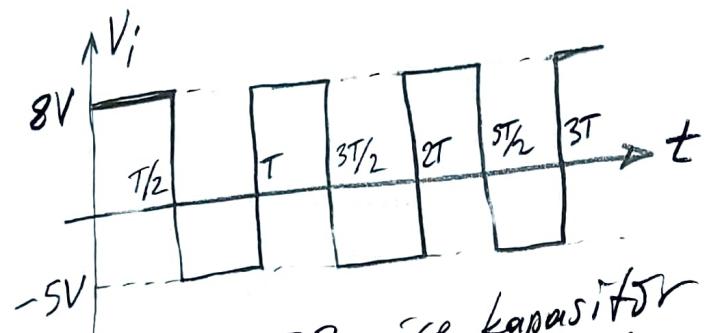


Kenetlenme Devresi

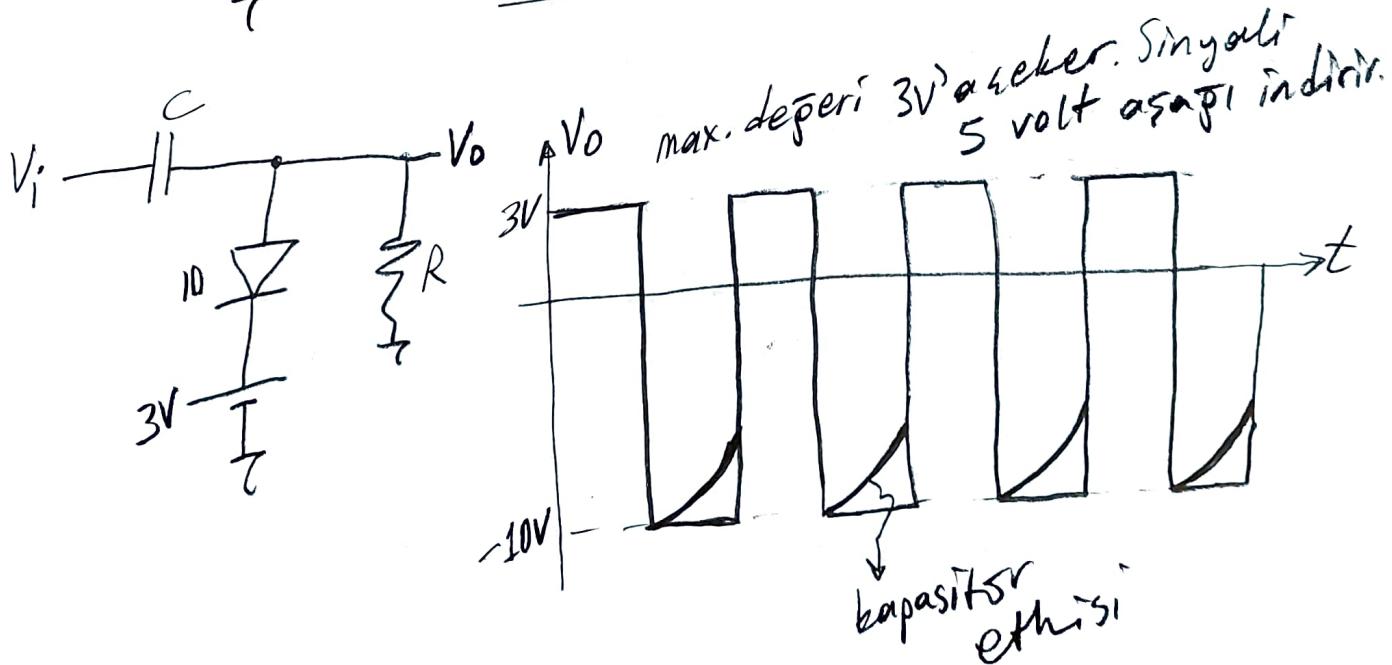
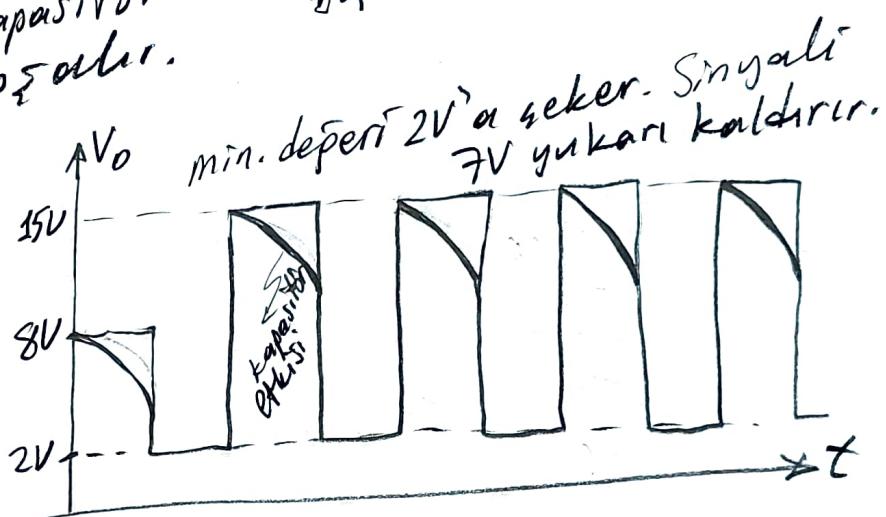
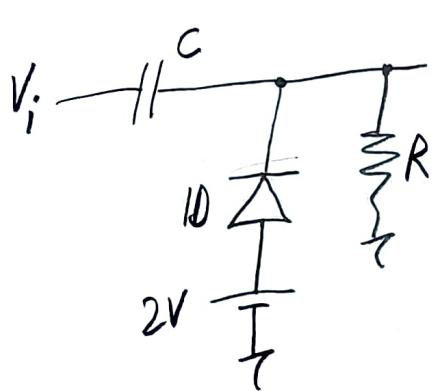
T : Periyot (sec) $f = \frac{1}{T}$
 f : Frekans (Hz)

$$T = RC \text{ Zaman Sabiti}$$

$5T$ Kapasitörün direnç
szerinden dolması ve
boşalması ızin gerekliliğe



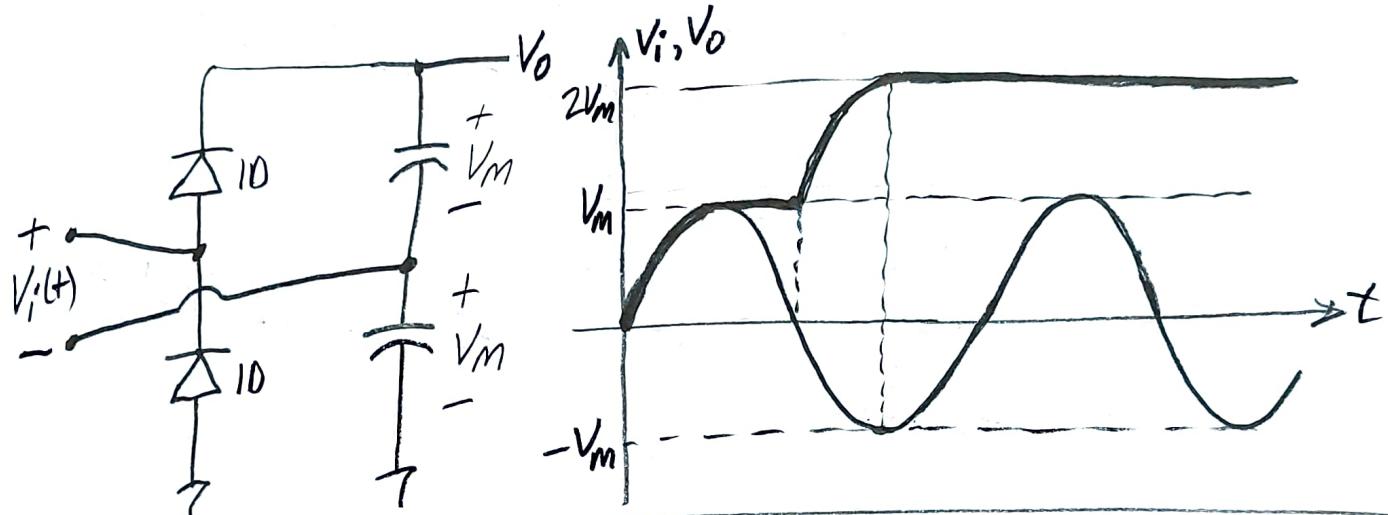
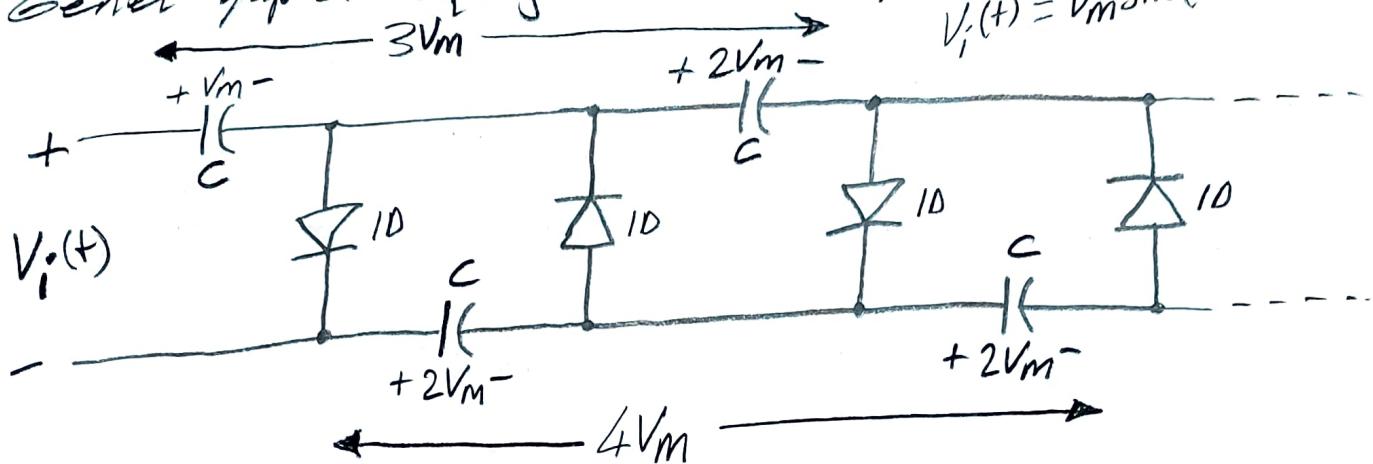
$T << 5T$ ise kapasitor
mzli dolar boşalar.



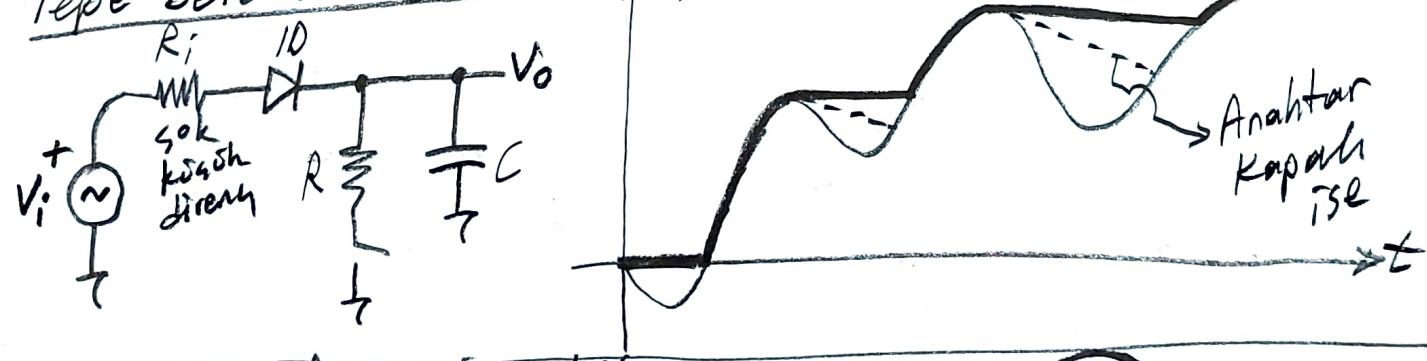
Gerilim Göklayıcı Devre

(29)

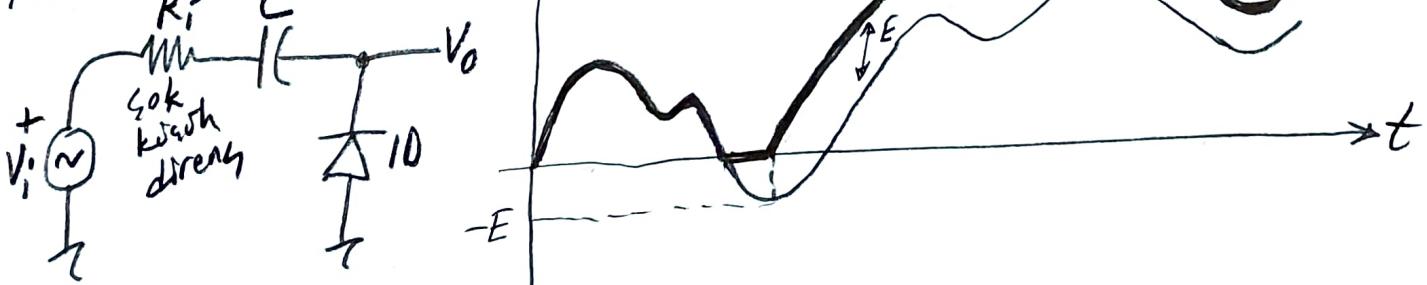
Girişine uygulanan AC geriliminin tepe değerinin katını gizsinda DC olarak veren devredir. Birleyici, İkileyici, Üçleyici gibi seşitleri vardır. Genel yapısı aşağıdaki verilmiştir.

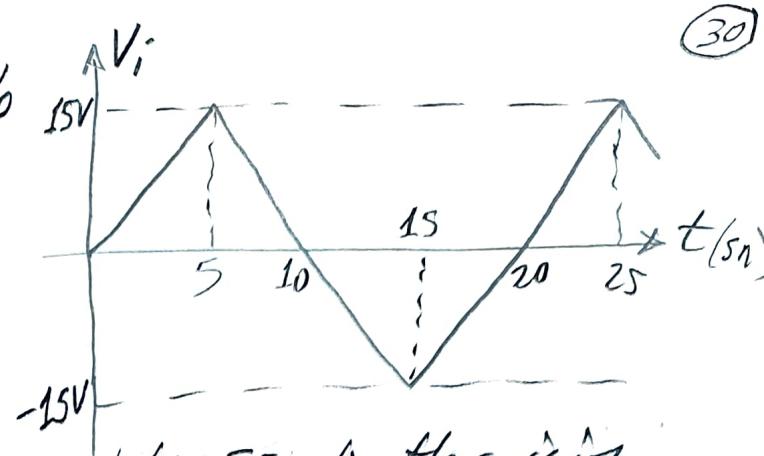
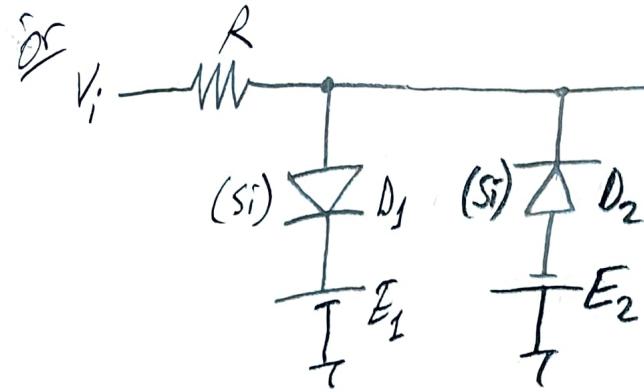


Tepe Detektörü Devresi



Kenetlenme Devresi





Yukarıda verilen kırımcı devresindeki Si diyođolar için
 $V_T = 0.7V$, $r_T = 0$ alınıyor. $R = 3k$, $I_{R\max} = 2mA$, $I_{R\min} = -3A$

- a) E_1 ve E_2 gerilimleri bulunuz.
- b) V_0 grafiğini çiziniz.
- c) Devrenin transfer karakteristikini çiziniz.

a) $i_{R\max} = 2mA$ için D_1 açık, D_2 kapalı
 $V_{0\max} = V_{\max} - R i_{R\max} = 15V - 3k \times 2mA = 15V - 6V = 9V$

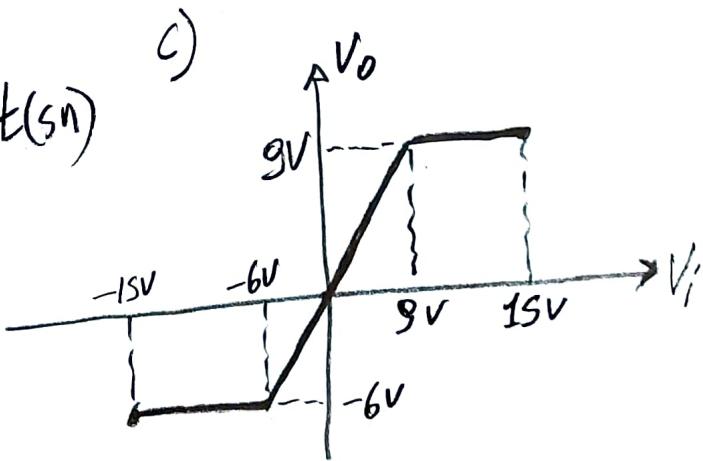
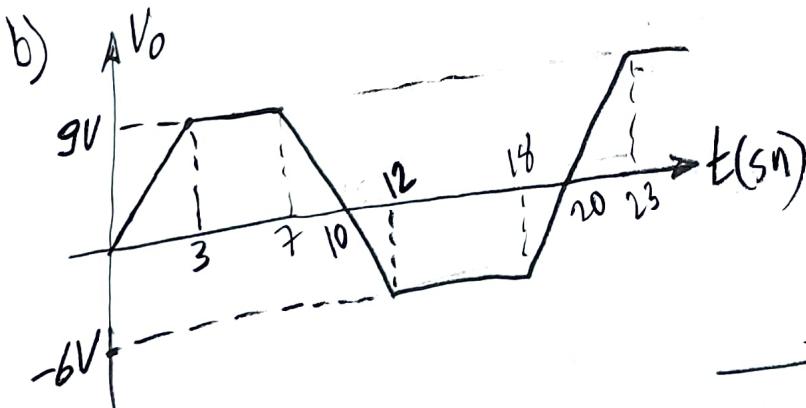
$$V_{0\max} = V_{\max} - V_T = 9V - 0.7V = 8.3V$$

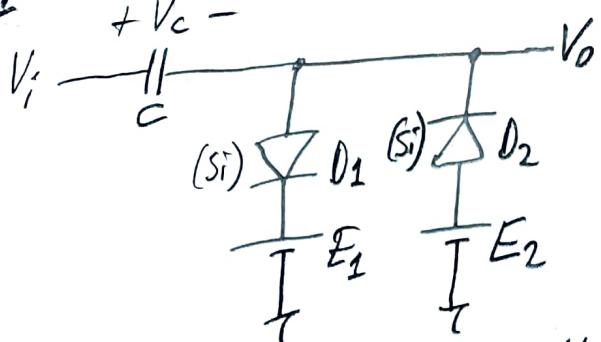
$E_1 = V_{0\max} - V_T = 9V - 0.7V = 8.3V$

$i_{R\min} = -3mA$ için D_2 açık, D_1 kapalı
 $V_{0\min} = V_{\min} - R i_{R\min} = -15V - 3k \times (-3mA) = -15V + 9V = -6V$

$$E_2 = -V_{0\min} - V_T = -(-6V) - 0.7V = 5.3V$$

$-6V \leq V_i \leq 9$ arasında D_1 ve D_2 kapalı $V_0 = V_i$ olur.



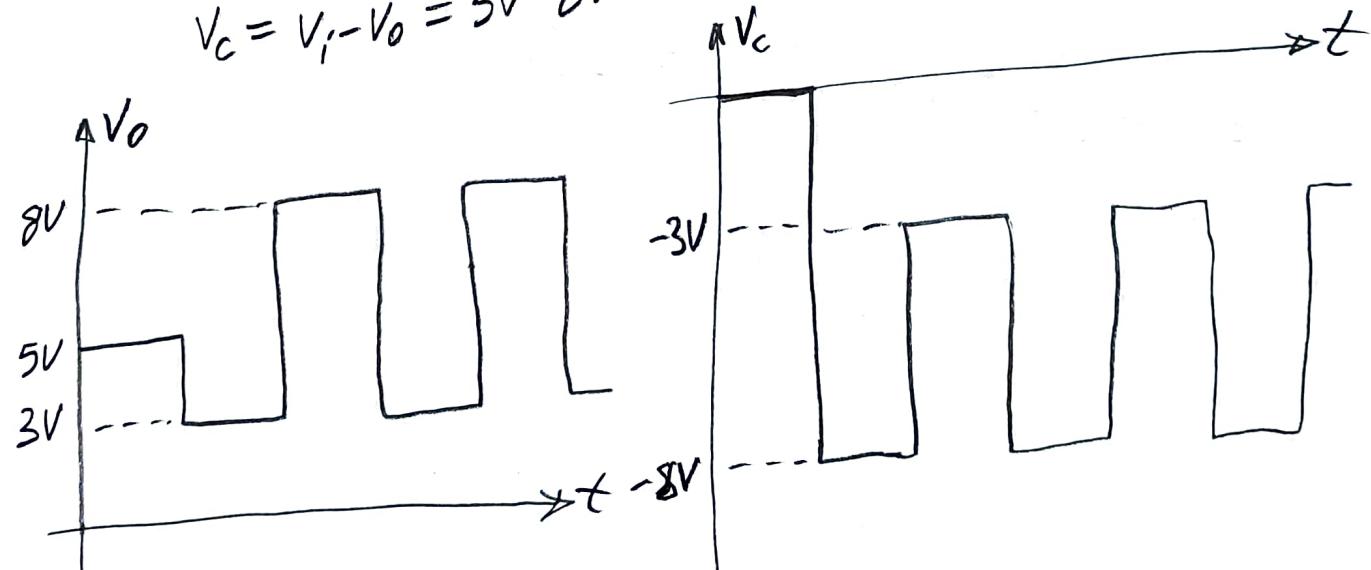


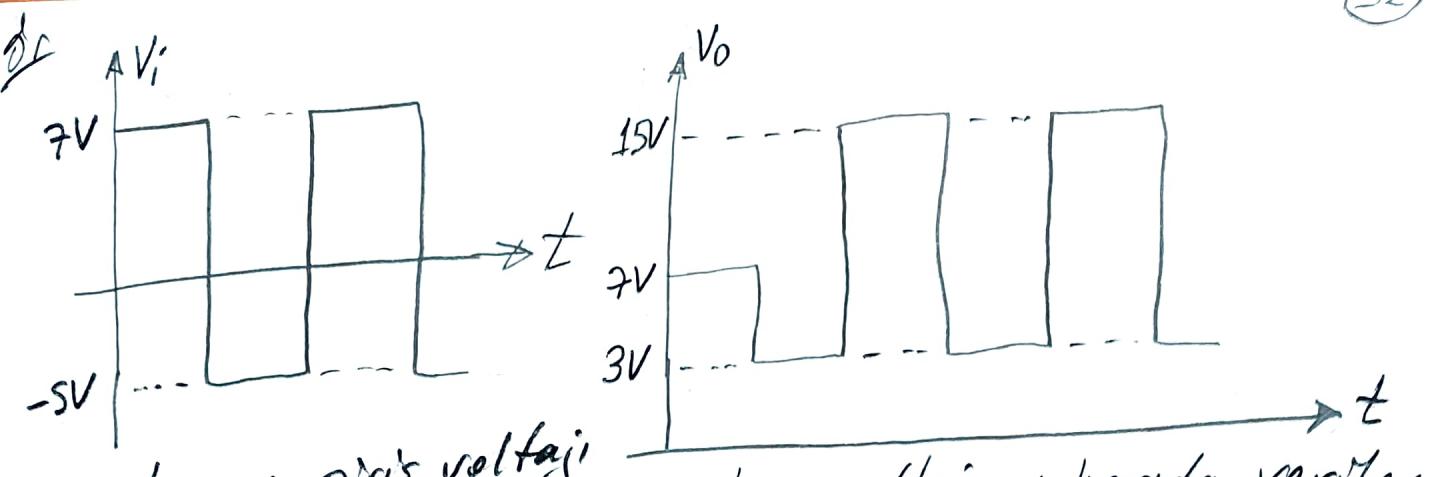
Yukarıda verilen kentetlenme devresindeki S_1 diyon
için $V_T = 0.7V$, $I_T = 0$ alınıyor.
 $E_1 = 7.3V$, $E_2 = 3.7V$ olsun. Hesaplamalar yapıp V_o ve V_C
gerilimlerinin grafiklerini çiziniz.

④ $V_i = 5V$ iğin
 $E_1 + V_T = 7.3V + 0.7V = 8V > V_i$ D_1 kapalı
 $E_2 - V_T = 3.7V - 0.7V = 3V < V_i$ D_2 kapalı
 $V_C = 0 \Rightarrow V_o = V_i - V_C = 5V$

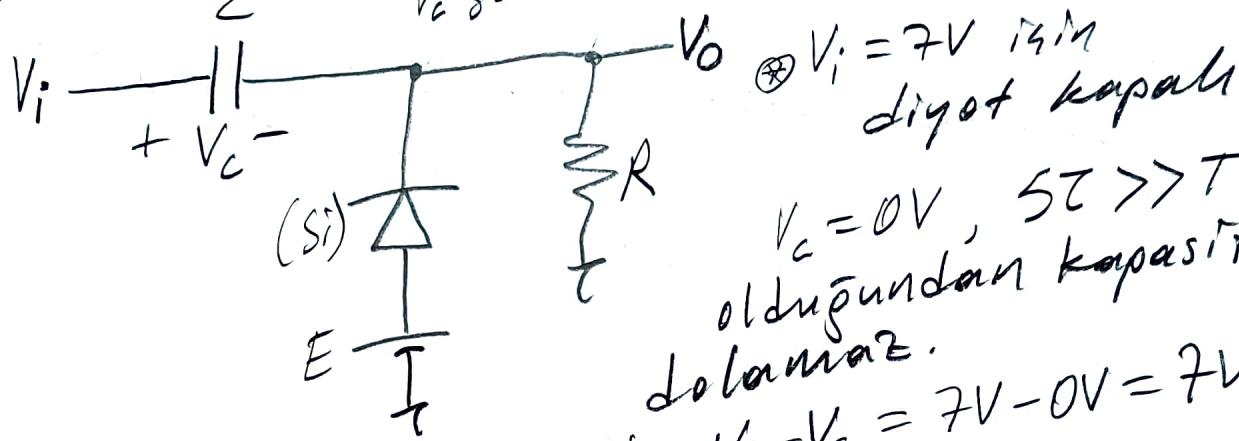
⑤ $V_i = -5V$ iğin
 D_1 kapalı, D_2 açık
 $V_o = E_2 - V_T = 3.7V - 0.7V = 3V$
 $V_C = V_i - V_o = -5V - 3V = -8V$

⑥ $V_i = 5V$ iğin
 D_1 açık, D_2 kapalı
 $V_o = E_1 + V_T = 7.3V + 0.7V = 8V$
 $V_C = V_i - V_o = 5V - 8V = -3V$





Vygulanan giriş volası
ve buna karşılık gelen çıkış volası yukarıda verilen
kenetlenme devresini Si diyot kullanarak tasarlayıniz.
Vc geriliminin grafiğini çiziniz.



$$\textcircled{1} \quad V_i = 7V \text{ iken diyot kapali}$$

$$V_c = 0V, ST \gg T$$

$$\text{olduguundan kapasitor dolanır.}$$

$$V_o = V_i - V_c = 7V - 0V = 7V$$

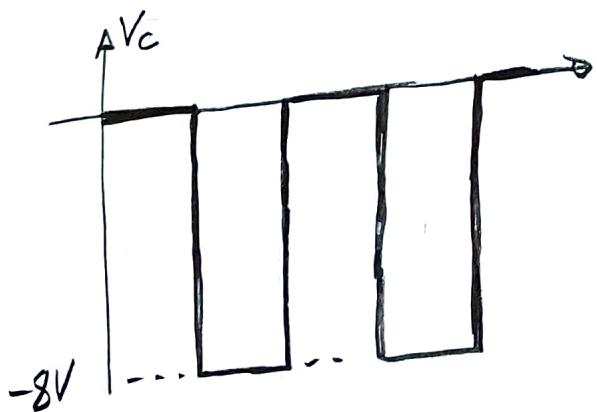
$\textcircled{2}$ $V_i = -5V$ iken diyot açık

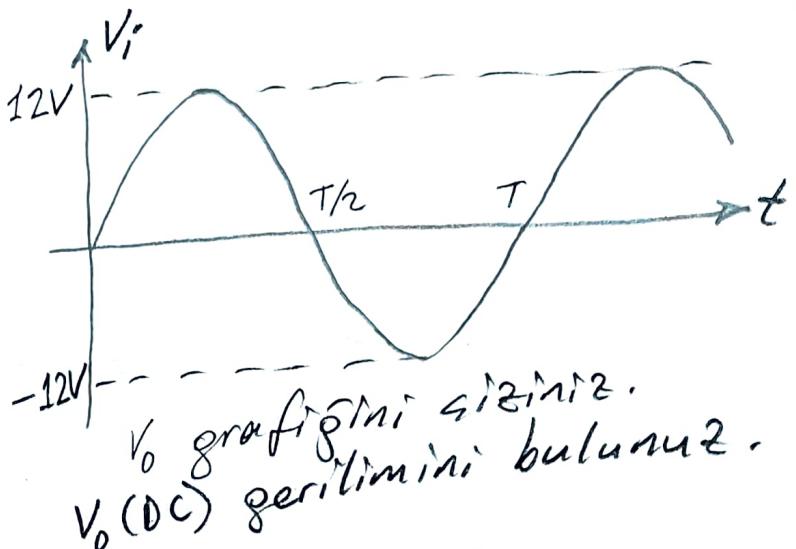
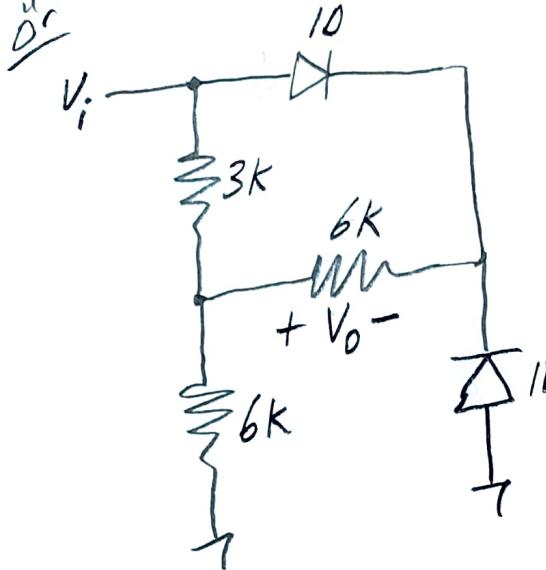
$$V_o = E - V_T = 3V \Rightarrow E = V_T + 3V = 3.7V$$

$$V_c = V_i - V_o = -5V - 3V = -8V$$

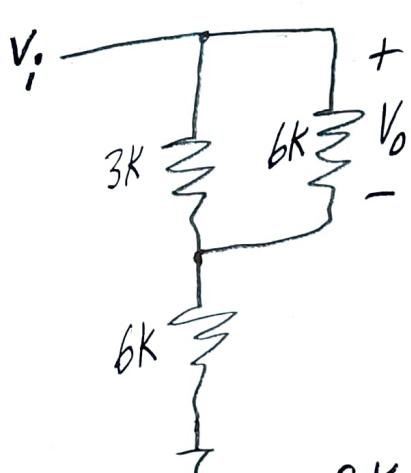
$\textcircled{3}$ $V_i = 7V$ iken diyot kapali.

$$V_o = V_i - V_c = 7V - (-8V) = 15V$$



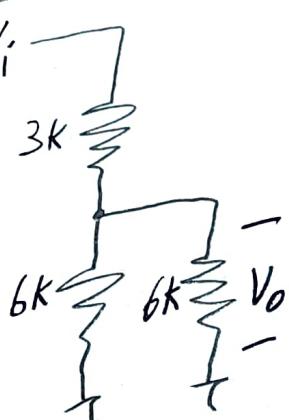


$V_i \geq 0$ i̇çin



$$V_i = \frac{V_0}{4}$$

$V_i < 0$ i̇çin



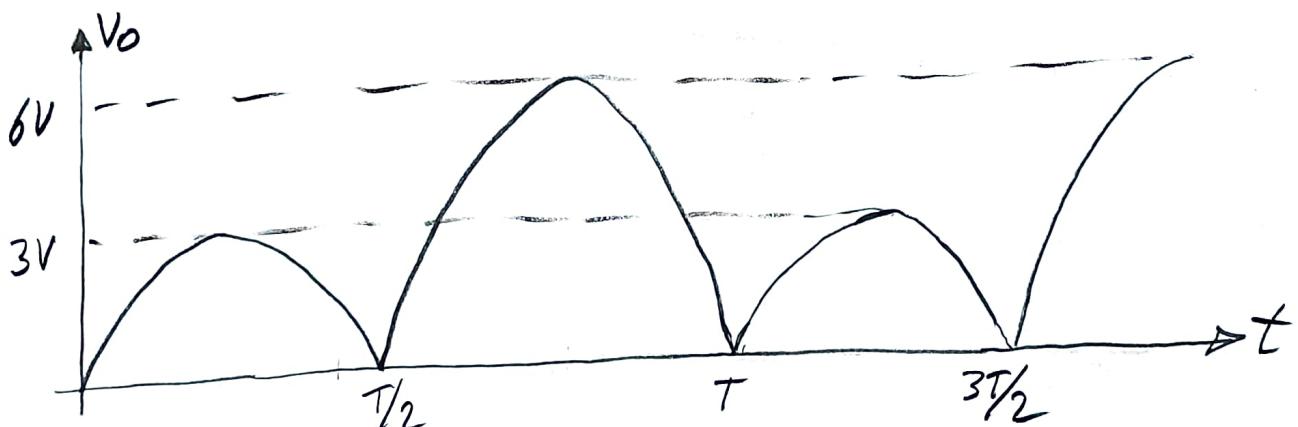
$$V_0 = -\frac{V_i}{2}$$

$$R_e = 3K // 6K = 2K$$

$$V_{0\max} = \frac{V_{imax}}{4} = \frac{12V}{4} = 3V$$

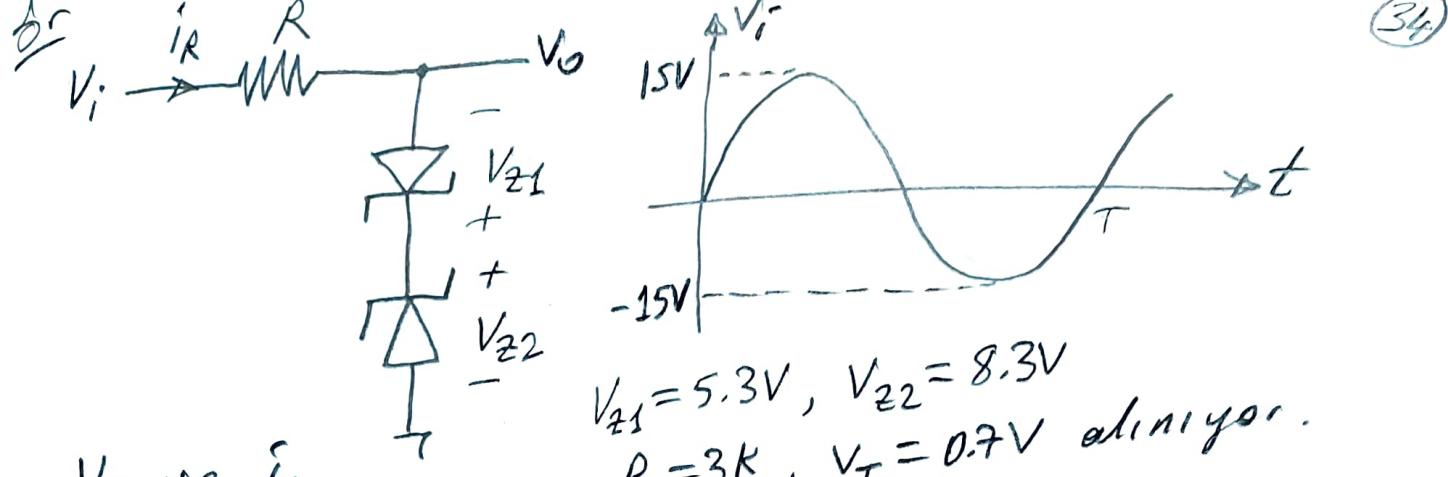
$$R_e = 6K // 6K = 3K$$

$$V_{0\max} = -\frac{V_{imax}}{2} = -\frac{12V}{2} = -6V$$



$$V_{DC} = 0.636 \times \left(\frac{3V + 6V}{2} \right) = 0.636 \times 4.5V$$

$$= 2.862V$$



V_o ve i_R grafiklerini çiz.

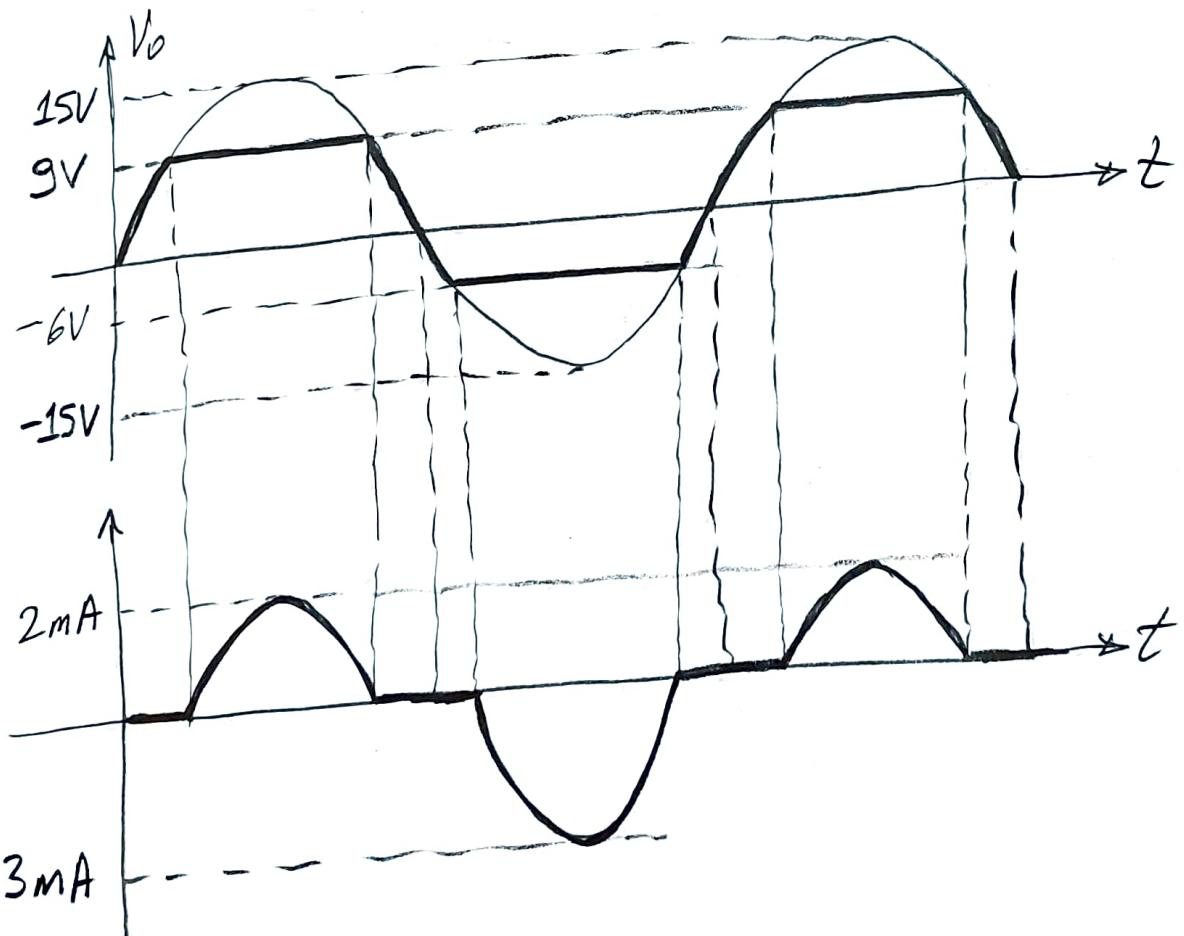
$$i_R = 0 \text{ iken } V_o = V_i$$

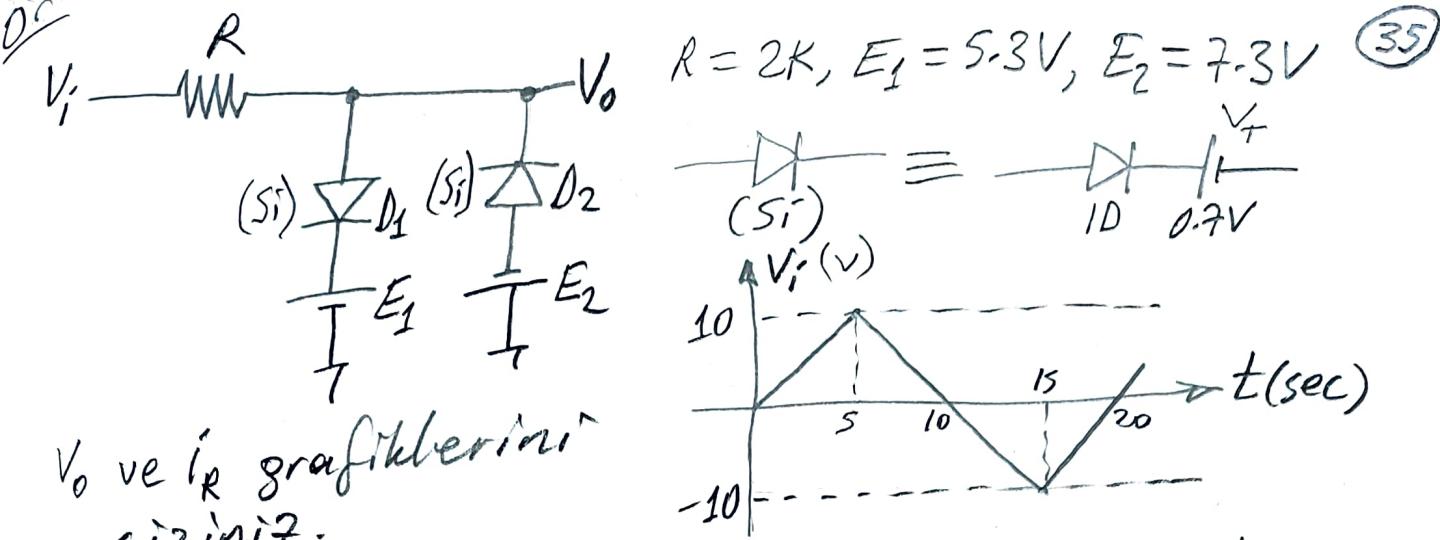
$$i_R > 0 \text{ iken } V_o = V_T + V_{z2} = 0.7V + 8.3V = 9V$$

$$i_{R\max} = \frac{V_{imax} - V_o}{R} = \frac{15V - 9V}{3k} = \frac{6V}{3k} = 2mA$$

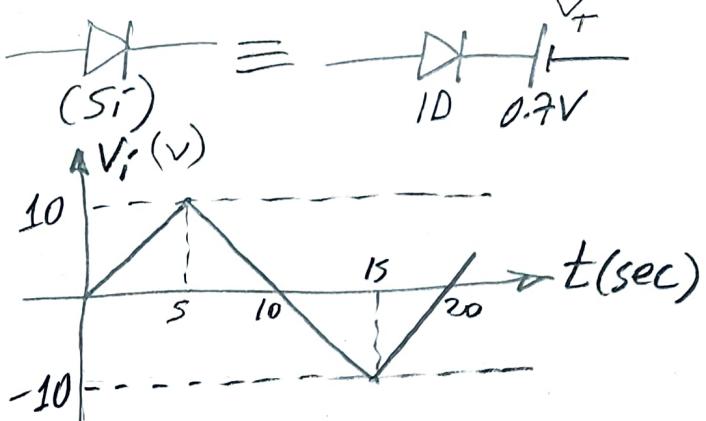
$$i_R < 0 \text{ iken } V_o = -V_{z1} - V_T = -5.3V - 0.7V = -6V$$

$$i_{R\min} = \frac{V_{imin} - V_o}{R} = \frac{-15V - (-6V)}{3k} = \frac{-9V}{3k} = -3mA$$





V_o ve i_R grafiklerini
giziniz.



$$E_1 + V_T = 5.3V + 0.7V = 6V, V_i \geq 6V \text{ ise } D_1 \text{ a\c{s}ik}$$

$$E_2 + V_T = 7.3V + 0.7V = 8V, V_i \leq -8V \text{ ise } D_2 \text{ a\c{s}ik.}$$

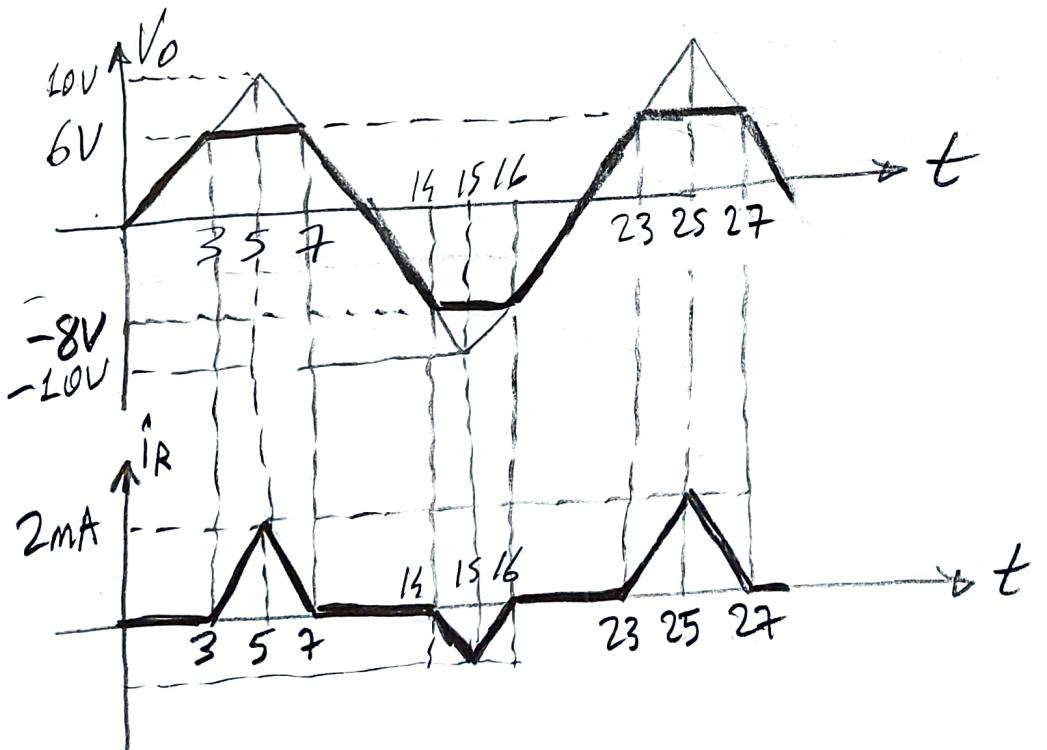
$-8V < V_i < 6V$ ise diyo\thar kapali $V_o = V_i, i_R = 0$

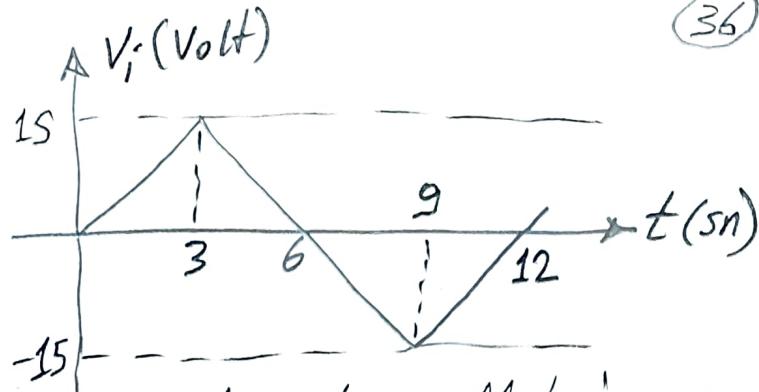
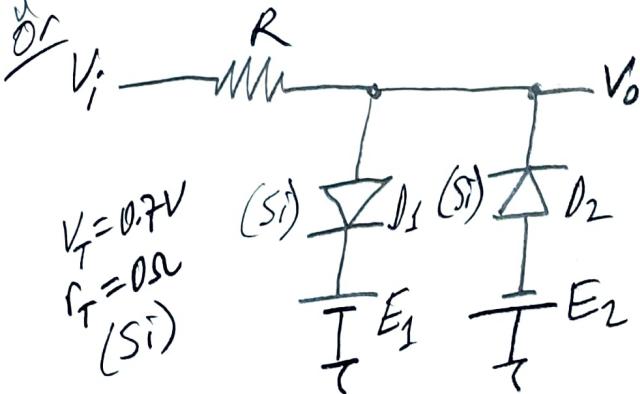
$\underline{V_i \geq 6V \text{ ise } D_1 \text{ a\c{s}ik, } D_2 \text{ kapali, } V_o = 6V}$

$$i_{Rmax} = \frac{V_{imax} - V_o}{R} = \frac{10V - 6V}{2K} = \frac{4V}{2K} = 2mA$$

$V_i \leq -8V \text{ ise } D_2 \text{ a\c{s}ik, } D_1 \text{ kapali, } V_o = -8V$

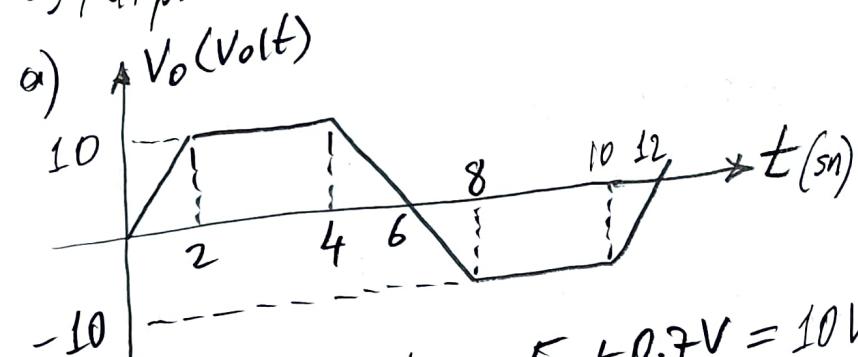
$$i_{Rmin} = \frac{V_{imin} - V_o}{R} = \frac{-10V - (-8V)}{2K} = \frac{-2V}{2K} = -1mA$$





Gökis Gerilimi $[-10, 10]$ aralığında olsun. Maksimum yörük akımı 10 mA olsun.

- V_o grafğini çiz.
- E_1, E_2, R değerlerini bulunuz.
- Kırıçılı devrenin transfer karakteristikini çiziniz.



3 sn'de 15V iner
veya gerekse
2 sn'de 10V iner
veya gerekse.

b) D_1 diyotu açıksa $E_1 + 0.7V = 10V$ olmalı

$$E_1 = 10V - 0.7V = 9.3V$$

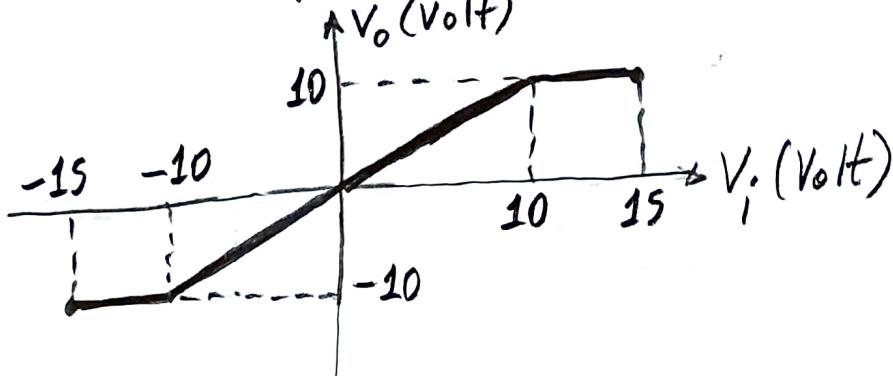
D_2 diyotu açıksa $-E_2 - 0.7V = -10V$ olmalı

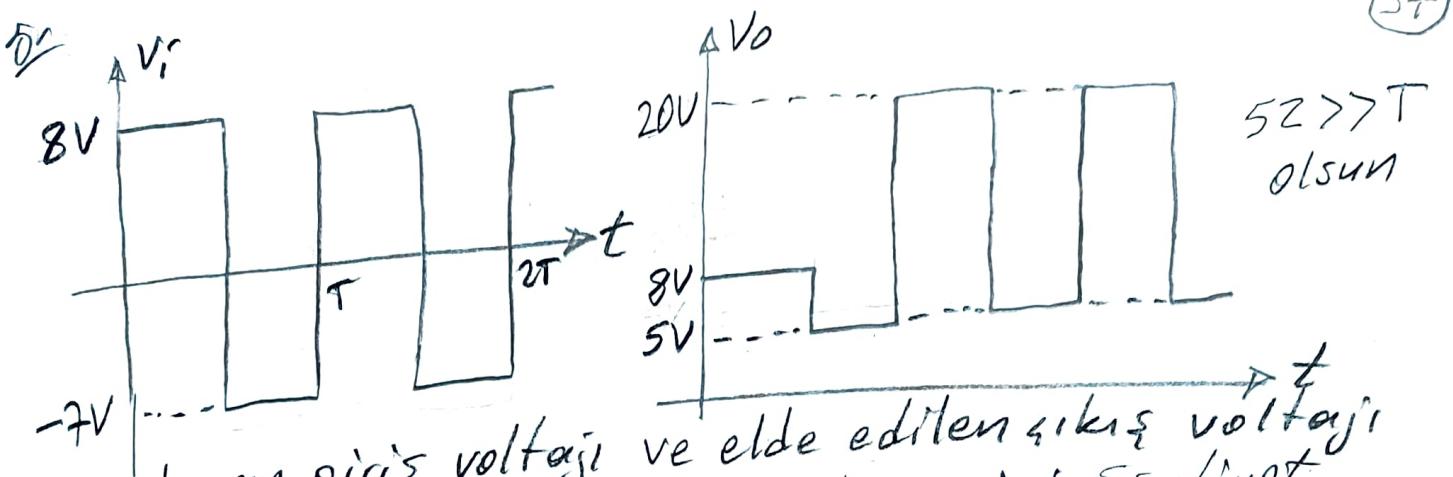
$$E_2 = 10V - 0.7V = 9.3V$$

$$R = \frac{V_{imax} - 10V}{I_{Rmax}} = \frac{15V - 10V}{10mA} = \frac{5V}{10mA} = 0.5K$$

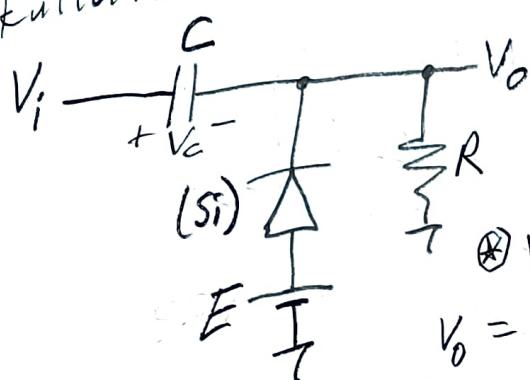
veya $R = \frac{-10V - V_{imin}}{I_{Rmax}} = \frac{-10V - (-15V)}{10mA} = \frac{5V}{10mA} = 0.5K$

c)





V_i giriş volajı ve elde edilen çıkış volajı yukarıda verilenken kenetlenme devresini Si diyot kullanarak tasarla.



④ $V_i = 8V$ için diyot kapalı.
 $V_o = V_i = 8V$, R direncinden dolayı kapasitor kısa sürede boşalamaz.

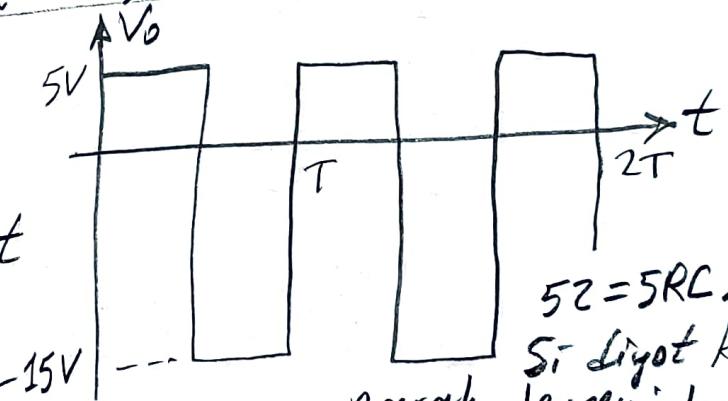
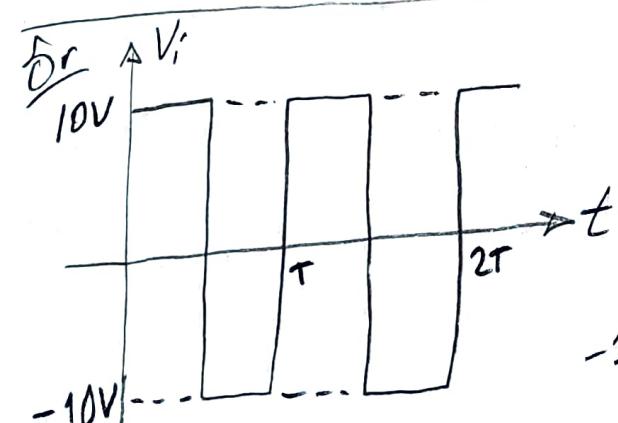
$$\text{④ } V_i = -7V \text{ için diyot açık.}$$

$$V_o = E - 0.7V = 5V \Rightarrow E = 5.7V$$

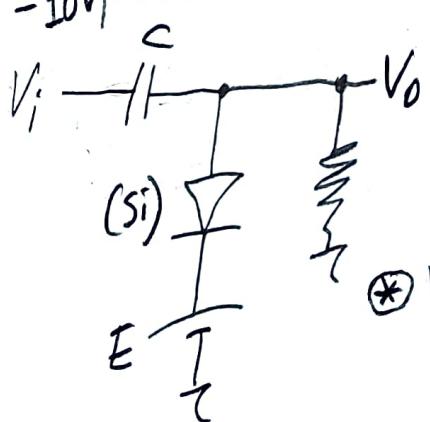
$$V_c = V_i - V_o = -7V - 5V = -12V$$

④ Diğer $V_i = 8V$ 'lar için diyot kapakları.

$$V_o = V_i - V_c = 8V - (-12V) = 20V$$



$5Z = 5RC >> T$
 Si diyot kullanarak devreyi tasarla.



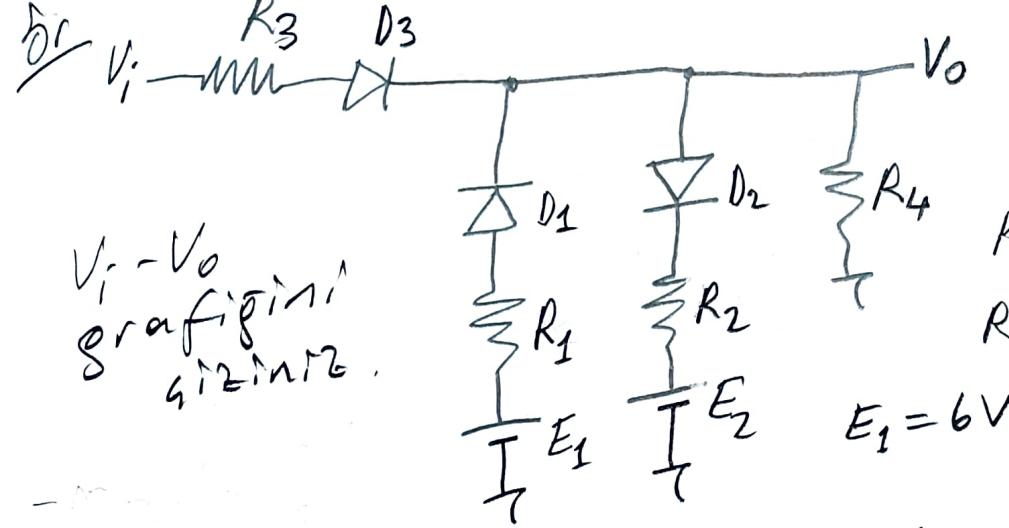
④ $V_i = 10V$ için diyot açık olur.

$$V_o = E + 0.7V = 5V \Rightarrow E = 4.3V$$

$$V_c = V_i - V_o = 10V - 5V = 5V$$

④ $V_i = -10V$ için diyot kapakları.

$$V_o = V_i - V_c = -10V - 5V = -15V$$



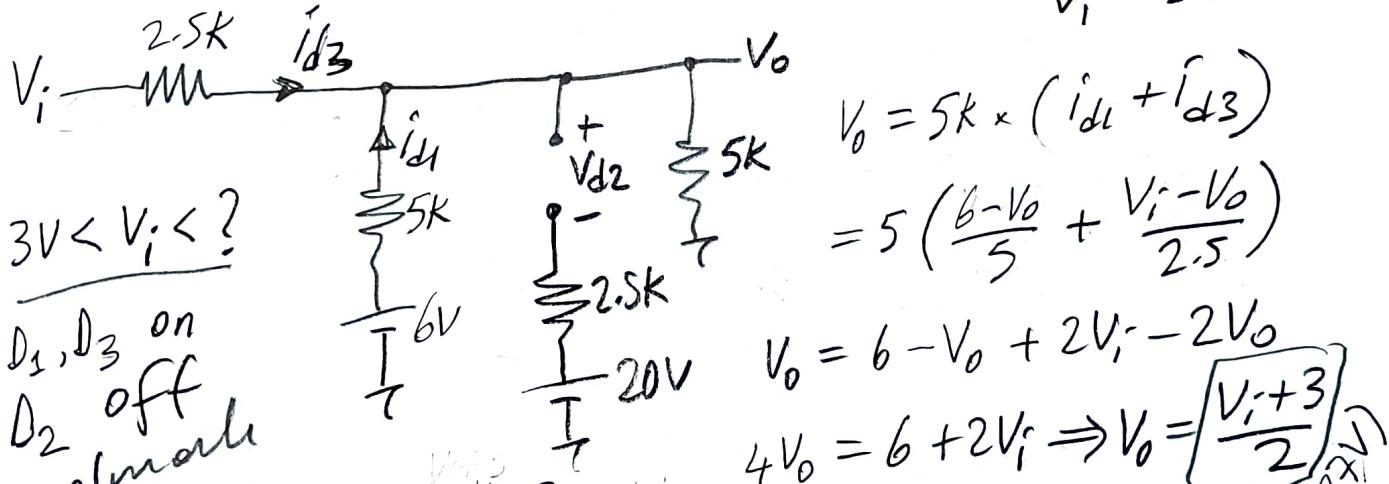
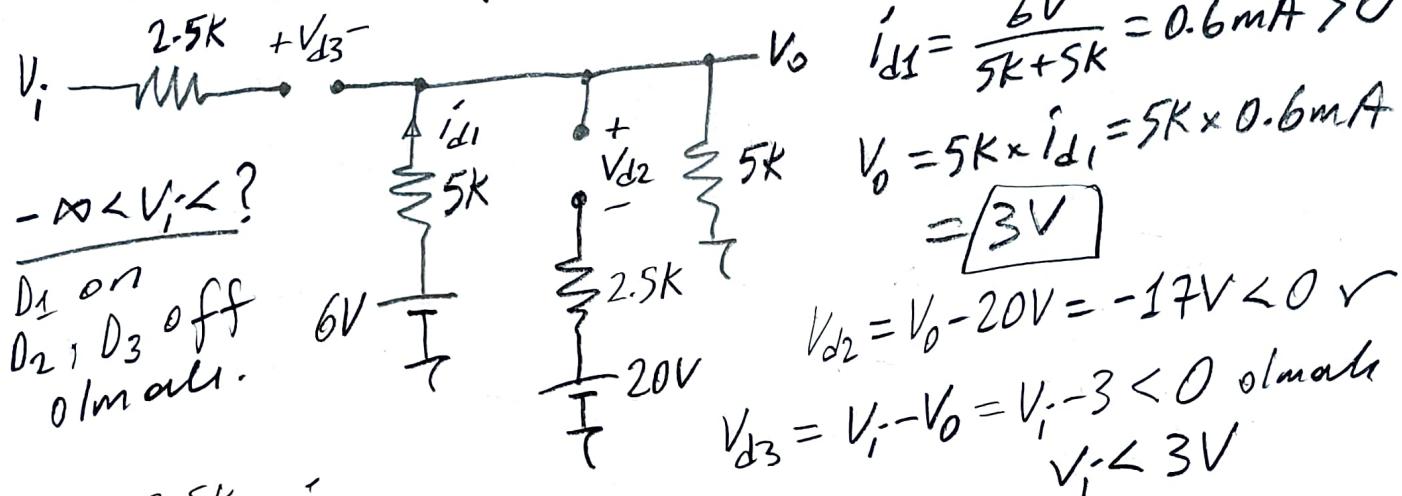
$V_i - V_o$
grafikini
grafikini

Tüm diyonlar
idealdir.

$$R_1 = R_4 = 5k$$

$$R_2 = R_3 = 2.5k$$

$$E_1 = 6V, E_2 = 20V$$



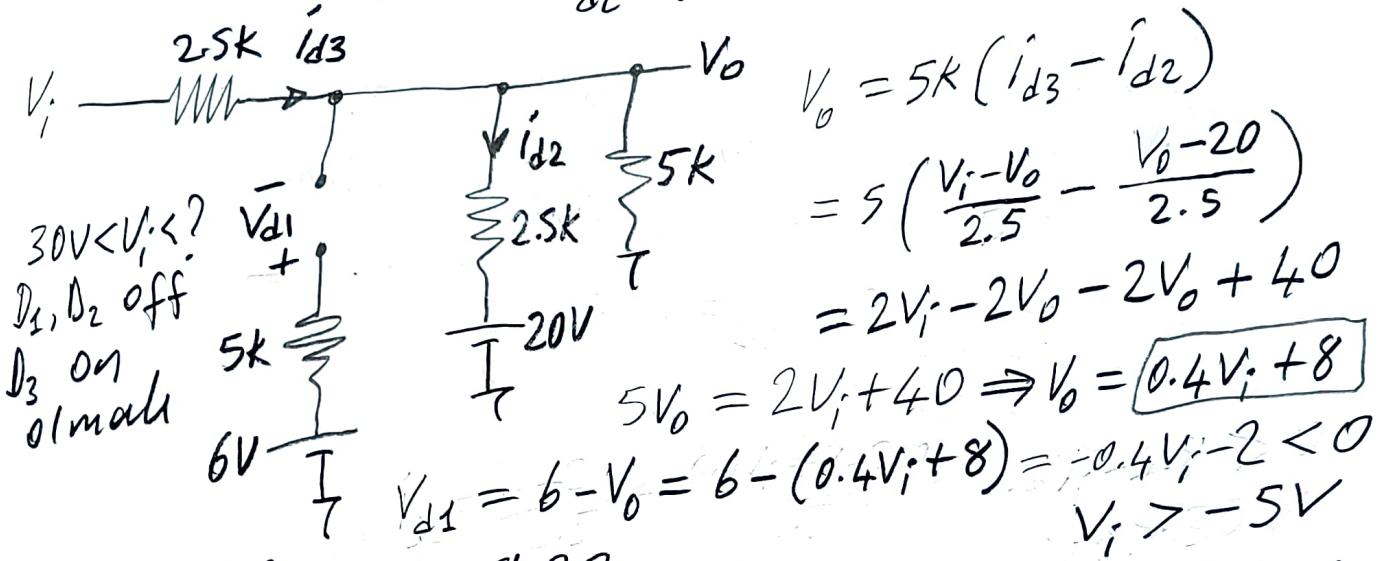
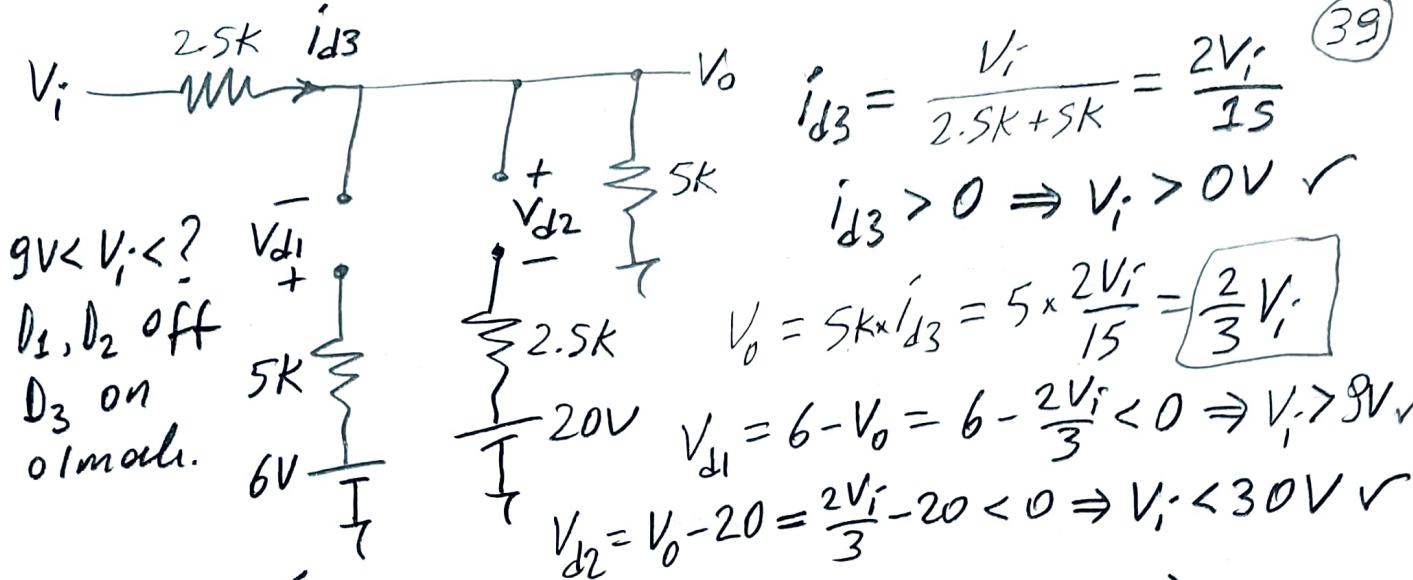
$$i_{d1} = \frac{6 - V_o}{5} = \frac{6 - \frac{V_i + 3}{2}}{5} = \frac{9 - V_i}{10} > 0 \Rightarrow V_i < 9V$$

$$V_{d2} = V_o - 20 = \frac{V_i + 3}{2} - 20 \Rightarrow \frac{V_i - 37}{2} < 0 \Rightarrow V_i < 37V$$

$$i_{d3} = \frac{V_i - V_o}{2.5} = \frac{V_i - \frac{V_i + 3}{2}}{2.5} = \frac{V_i - 3}{6} > 0 \Rightarrow V_i > 3V$$

2 diper sayfa

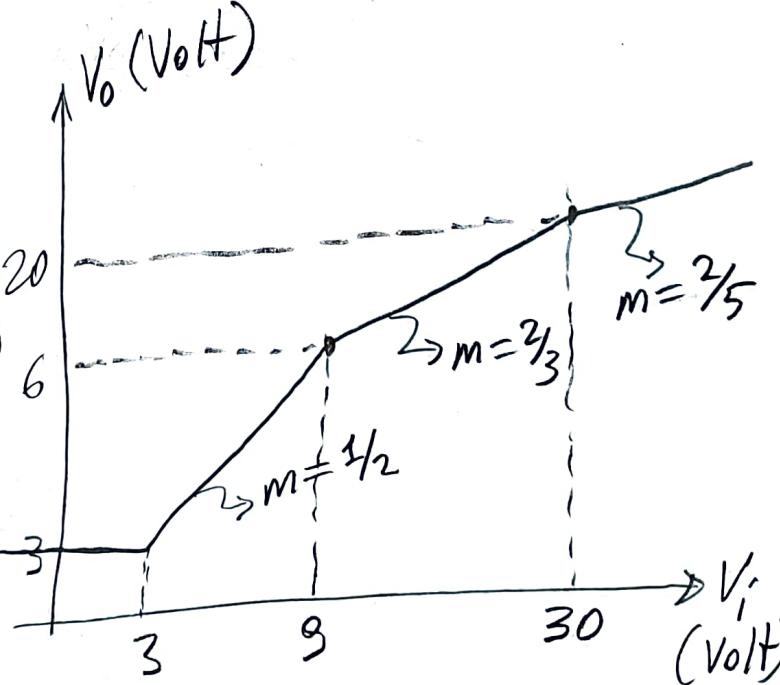
(39)

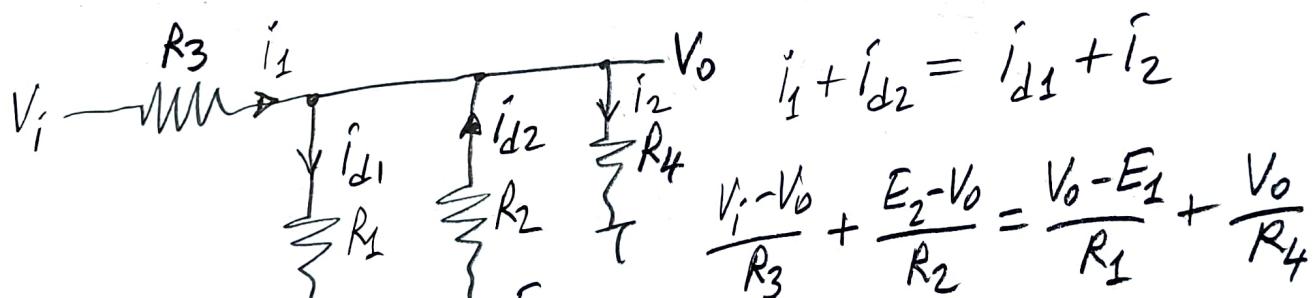
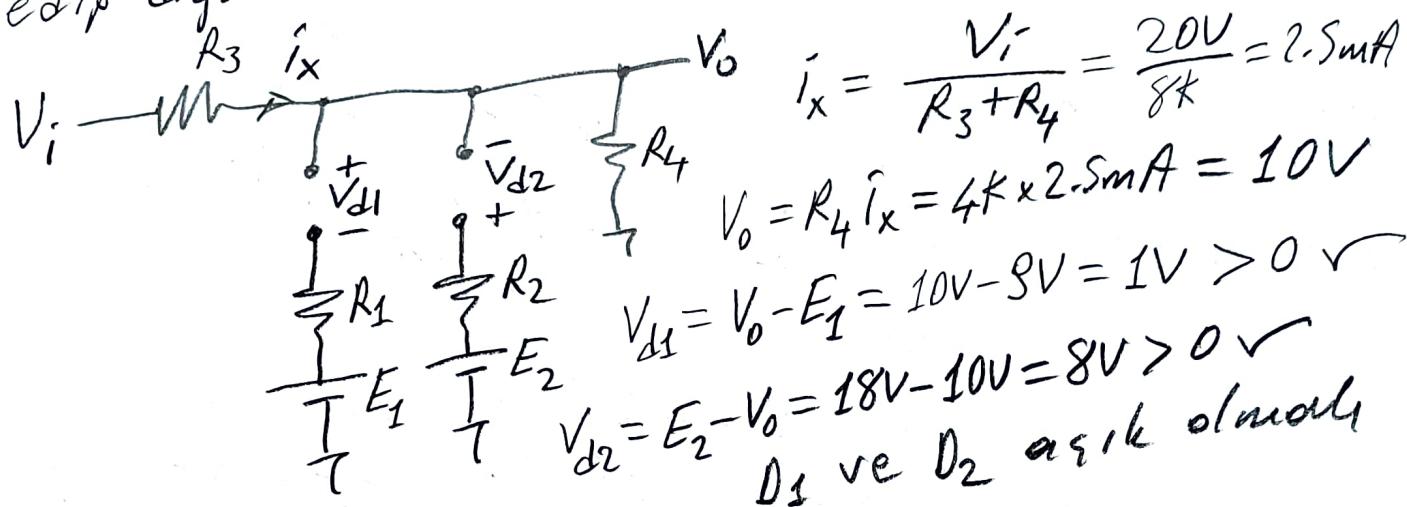
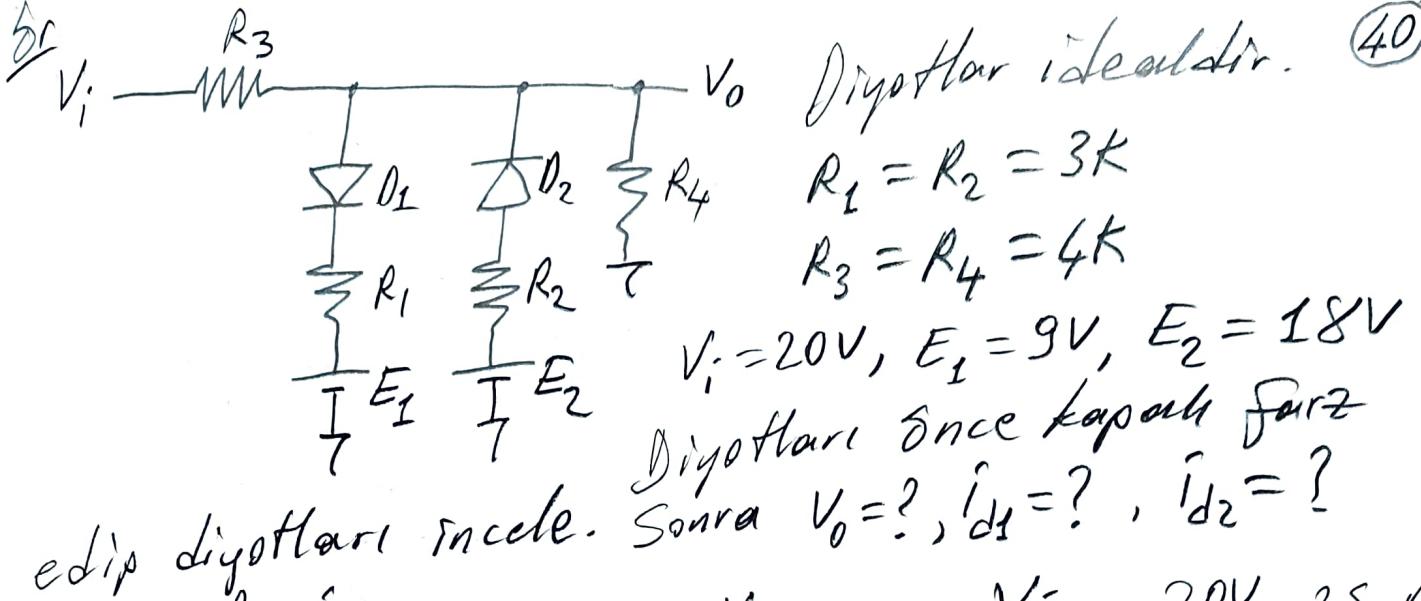


$$i_{d2} = \frac{V_o - 20}{2.5} = \frac{0.4V_i + 8 - 20}{2.5} = 0.16V_i - 4.8 > 0 \Rightarrow V_i > 30V$$

$$i_{d3} = \frac{V_i - V_o}{2.5} = \frac{V_i - (0.4V_i + 8)}{2.5} = 0.24V_i - 3.2 > 0 \Rightarrow V_i > \frac{40}{3}V$$

$$V_o = \begin{cases} 3 & V_i < 3 \\ \frac{V_i + 3}{2} & 3 \leq V_i < 9 \\ \frac{2V_i}{3} & 9 \leq V_i < 30 \\ \frac{2V_i + 40}{5} & V_i > 30 \end{cases}$$





$$\frac{20 - V_0}{4} + \frac{18 - V_0}{3} = \frac{V_0 - 9}{3} + \frac{V_0}{4}$$

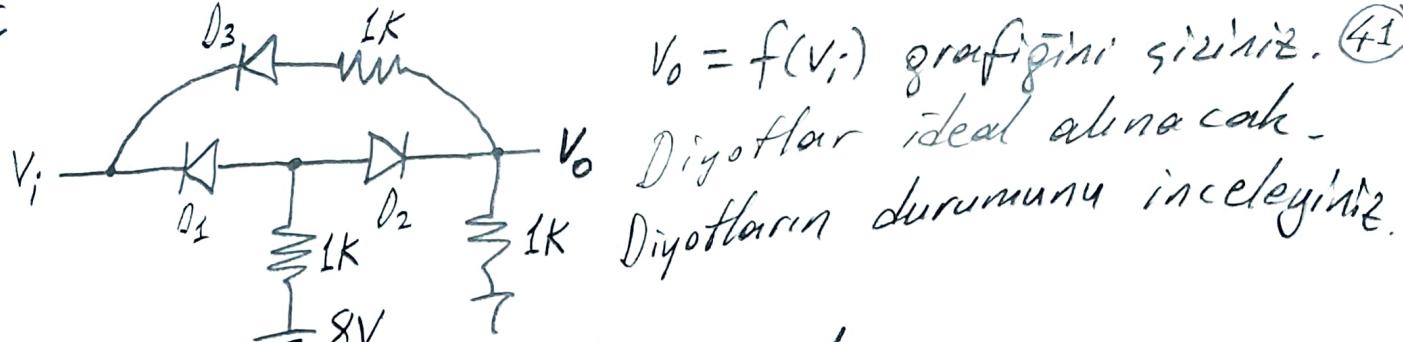
$$5 - \frac{V_0}{4} + 6 - \frac{V_0}{3} = \frac{V_0}{3} - 3 + \frac{V_0}{4}$$

$$\frac{2V_0}{3} + \frac{2V_0}{4} = 5 + 6 + 3 \Rightarrow \frac{14V_0}{12} = 14 \Rightarrow V_0 = 12\text{V}$$

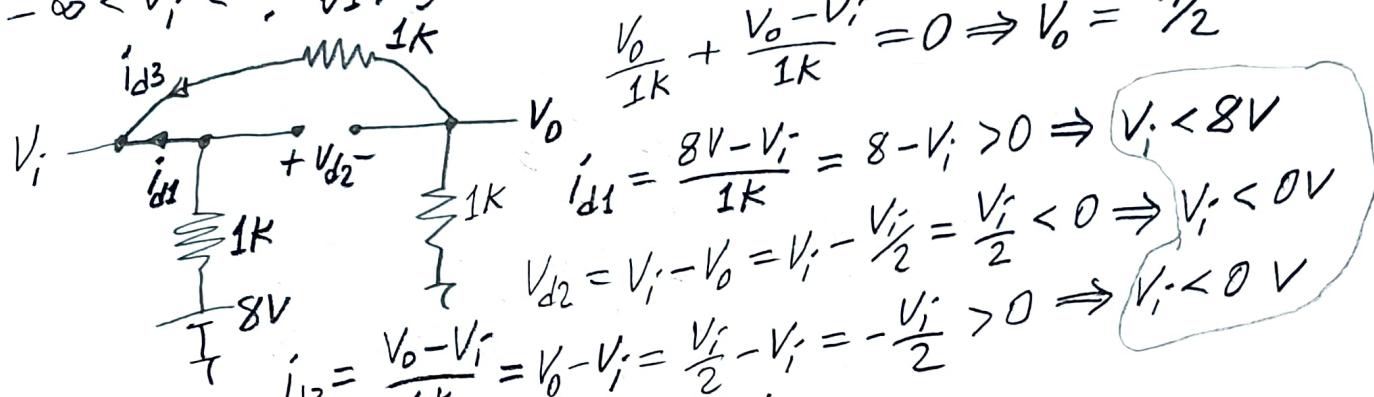
$$(4) \quad (3) \quad i_{d1} = \frac{V_0 - E_1}{R_1} = \frac{12\text{V} - 9\text{V}}{3\text{K}} = \frac{3\text{V}}{3\text{K}} = 1\text{mA} > 0$$

$$i_{d2} = \frac{E_2 - V_0}{R_2} = \frac{18\text{V} - 12\text{V}}{3\text{K}} = \frac{6\text{V}}{3\text{K}} = 2\text{mA} > 0$$

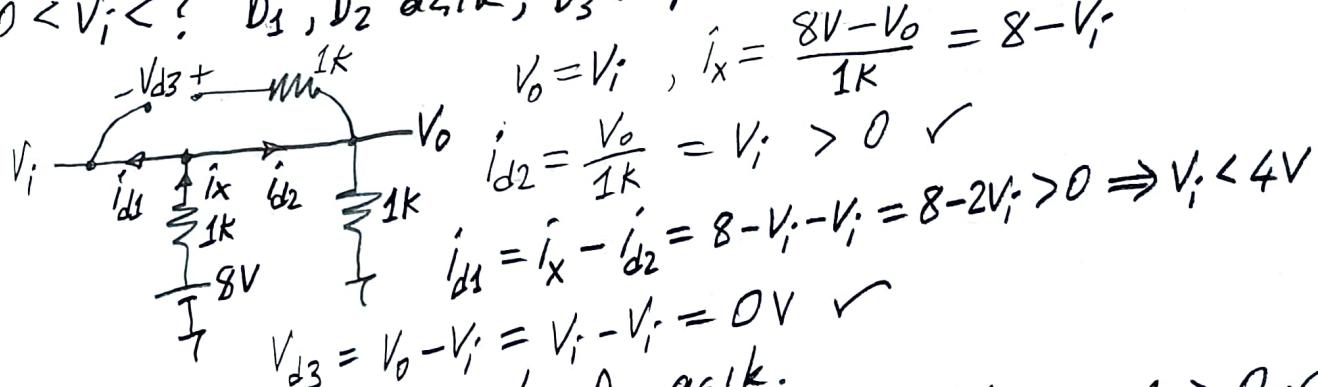
$$i_{d2} = \frac{E_2 - V_0}{R_2} = \frac{18\text{V} - 12\text{V}}{3\text{K}} = \frac{6\text{V}}{3\text{K}} = 2\text{mA} > 0$$



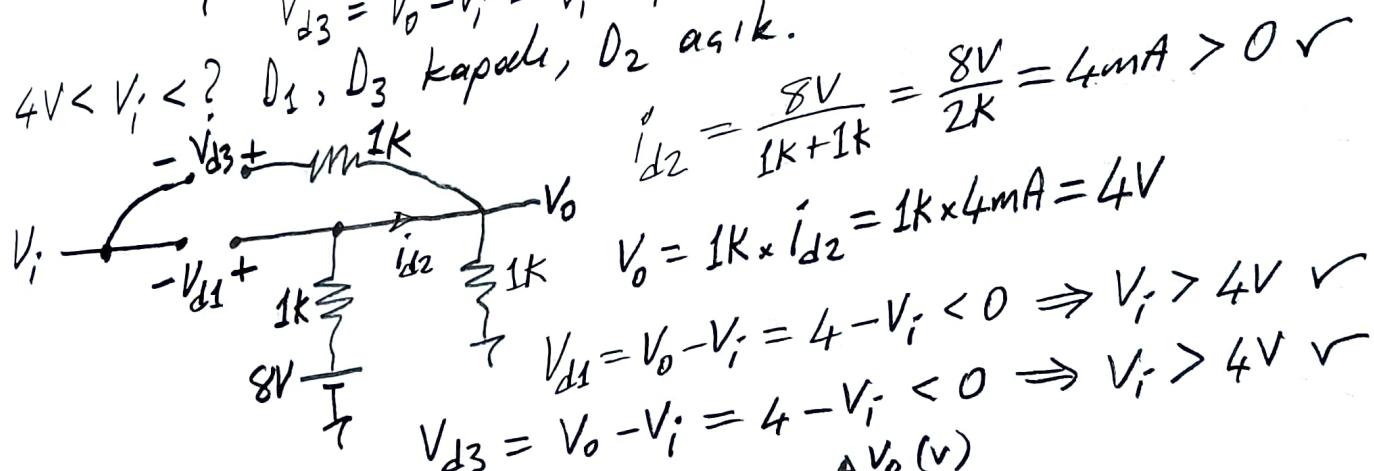
$-\infty < V_i < ?$ D_1, D_3 açıktır, D_2 kapalı



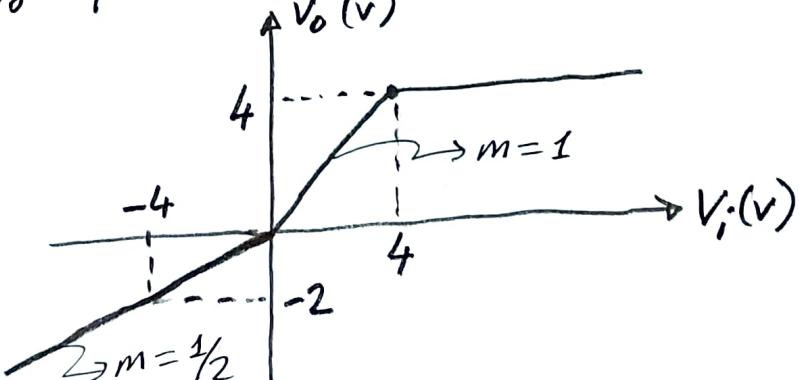
$0 < V_i < ?$ D_1, D_2 açıktır, D_3 kapalı

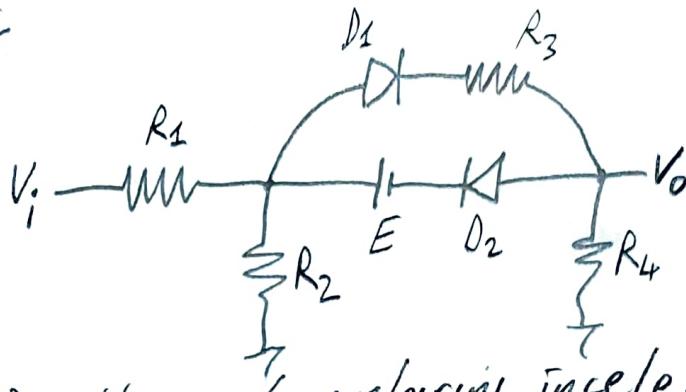


$4V < V_i < ?$ D_1, D_3 kapalı, D_2 açıktır.



$$V_o = \begin{cases} \frac{V_i}{2}, & V_i < 0 \\ V_i, & 0 \leq V_i < 4V \\ 4, & V_i \geq 4V \end{cases}$$





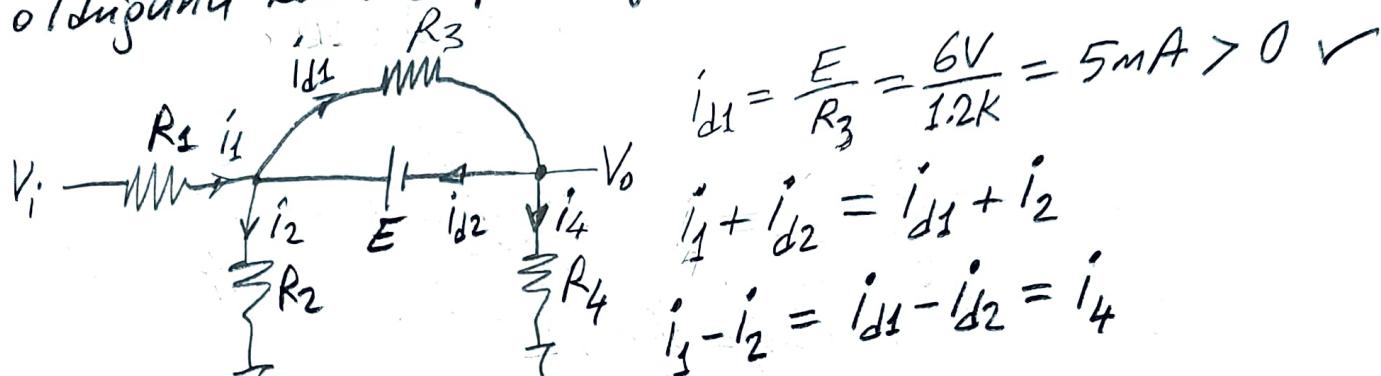
$$V_i = 24V, E = 6V$$

$$R_1 = 2K, R_2 = 8K$$

$$R_3 = 1.2K, R_4 = 5K$$

Diyotlar idealdir.

Diyotların durumlarını incelemeden diyotların asılık olduğunu kabul edip soruyu çöz. $V_o, i_{d1}, i_{d2}, V_{d1}, V_{d2} = ?$



$$i_{d1} = \frac{E}{R_3} = \frac{6V}{1.2K} = 5mA > 0 \quad \checkmark$$

$$i_1 + i_{d2} = i_{d1} + i_2$$

$$i_3 - i_2 = i_{d1} - i_{d2} = i_4$$

$$\frac{V_i - E - V_o}{R_1} - \frac{E + V_o}{R_2} = \frac{V_o}{R_4}$$

$$\frac{24V - 6V - V_o}{2K} - \frac{6V + V_o}{8K} - \frac{V_o}{5K} = 0 \Rightarrow 9 - \frac{V_o}{2} - \frac{3}{4} - \frac{V_o}{8} - \frac{V_o}{5} = 0$$

$$(20) \quad \frac{V_o}{2} + \frac{V_o}{8} + \frac{V_o}{5} = \frac{33}{4} \Rightarrow \frac{33V_o}{40} = \frac{33}{4} \Rightarrow V_o = 10V$$

$$i_1 = \frac{V_i - E - V_o}{R_1} = \frac{24V - 6V - 10V}{2K} = \frac{8V}{2K} = 4mA$$

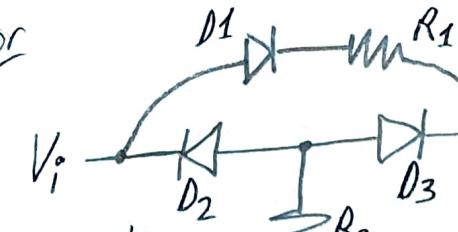
$$i_2 = \frac{E + V_o}{R_2} = \frac{6V + 10V}{8K} = \frac{16V}{8K} = 2mA$$

$$i_4 = \frac{V_o}{R_4} = \frac{10V}{5K} = 2mA$$

$$i_{d2} = i_{d1} - i_4 = 5mA - 2mA = 3mA$$

$$V_{d1} = 0V$$

$$V_{d2} = 0V$$

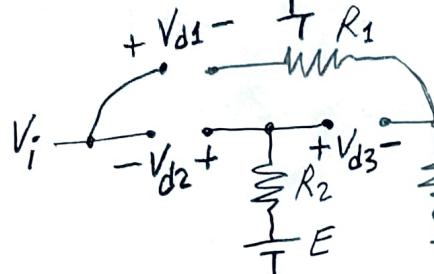


Diyotlar idealdir.

$$V_i = 15V, E = 12V, R_1 = 2k$$

$$R_2 = 1.5k, R_3 = 1.8k \text{ alınıyor.}$$

Once diyotları kapatı farz edip diyotların durumunu incele. Sonra yeni duruma göre diyotları incele. $V_o = ?$

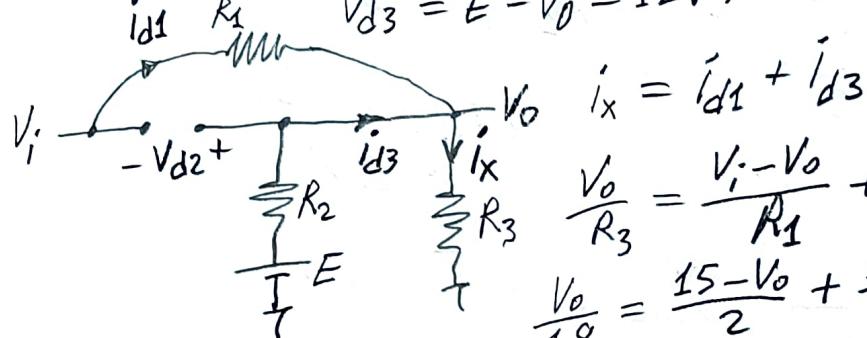


$$V_o = 0V$$

$$V_{d1} = V_i - V_o = 15V > 0, D_1 \text{ açık olmalı.}$$

$$V_{d2} = E - V_i = 12V - 15V = -3V < 0 \checkmark$$

$$V_{d3} = E - V_o = 12V > 0, D_3 \text{ açık olmalı.}$$



$$i_x = i_{d1} + i_{d3}$$

$$\frac{V_o}{R_3} = \frac{V_i - V_o}{R_1} + \frac{E - V_o}{R_2}$$

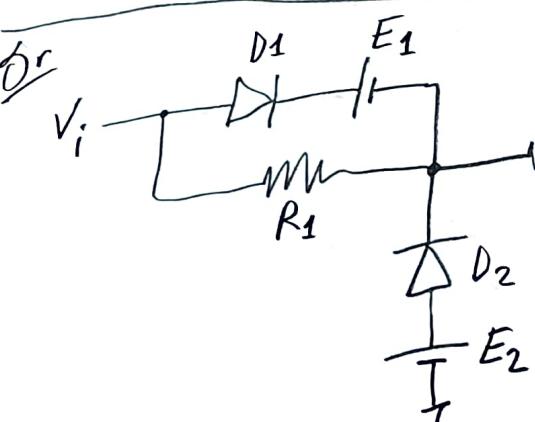
$$\frac{V_o}{1.8} = \frac{15 - V_o}{2} + \frac{12 - V_o}{1.5}, 18 \text{ ile çarp}$$

$$10V_o = 135 - 9V_o + 144 - 12V_o \Rightarrow 31V_o = 279 \Rightarrow V_o = 9V$$

$$i_{d1} = \frac{V_i - V_o}{R_1} = \frac{15V - 9V}{2k} = \frac{6V}{2k} = 3mA > 0 \checkmark$$

$$V_{d2} = V_o - V_i = 9V - 15V = -6V < 0 \checkmark$$

$$i_{d3} = i_x - i_{d1} = \frac{V_o}{R_3} - i_{d1} = \frac{9V}{1.8k} - 3mA = 5mA - 3mA = 2mA > 0 \checkmark$$



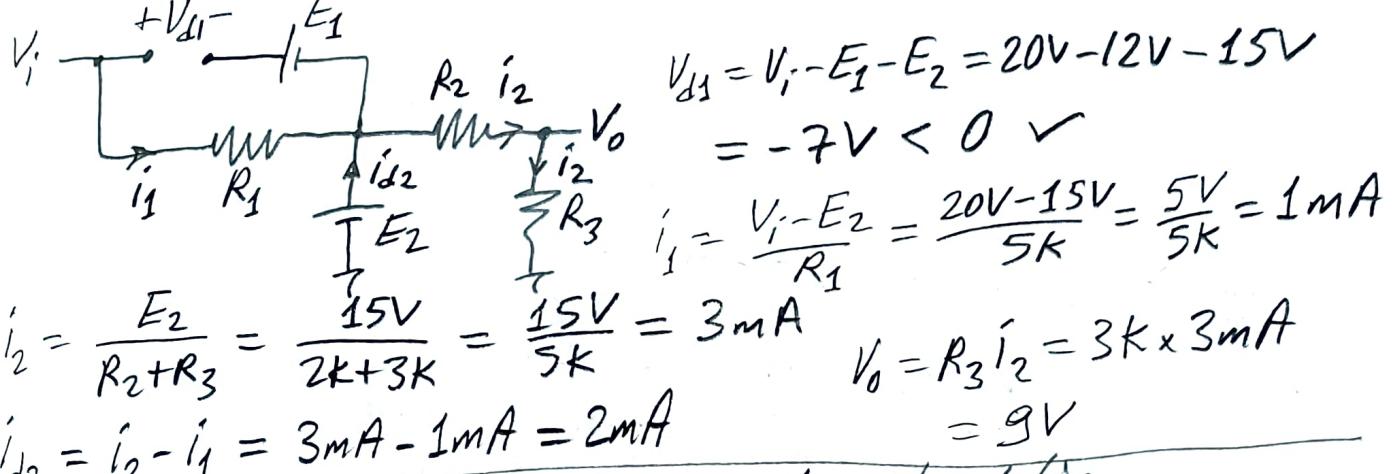
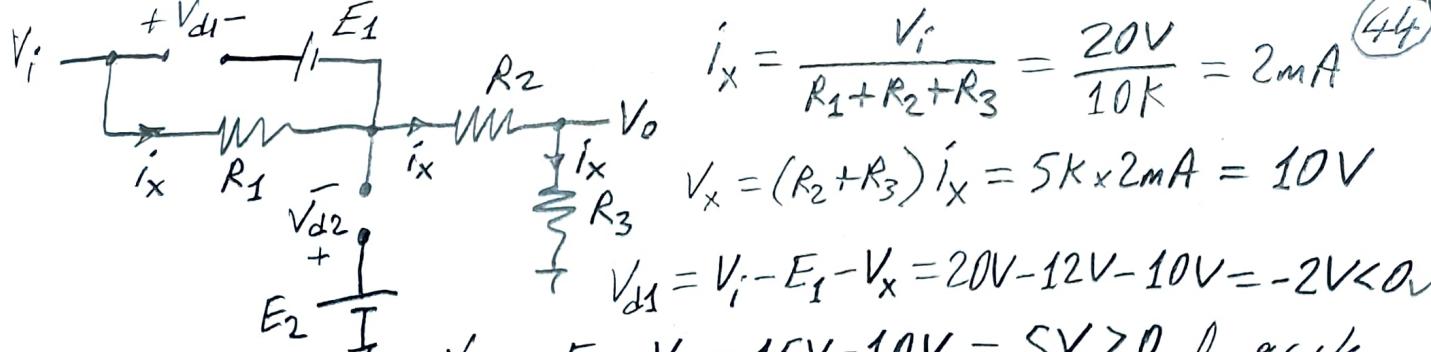
$$V_i = 20V, E_1 = 12V$$

$$E_2 = 15V, R_1 = 5k$$

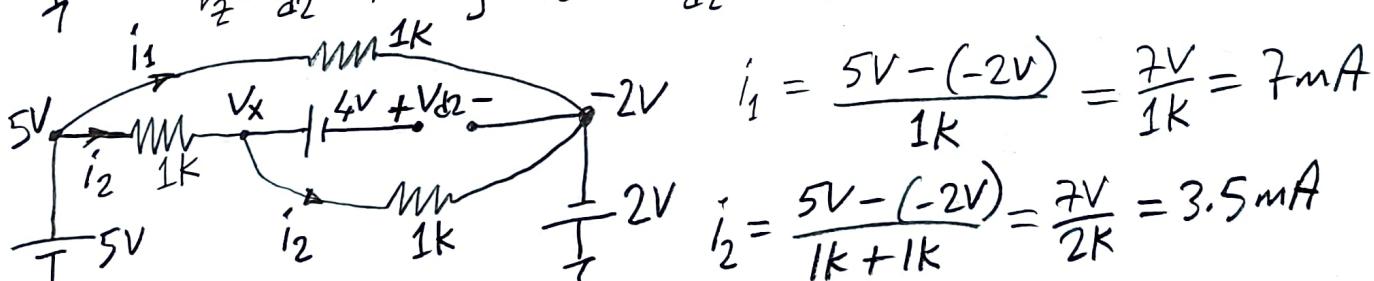
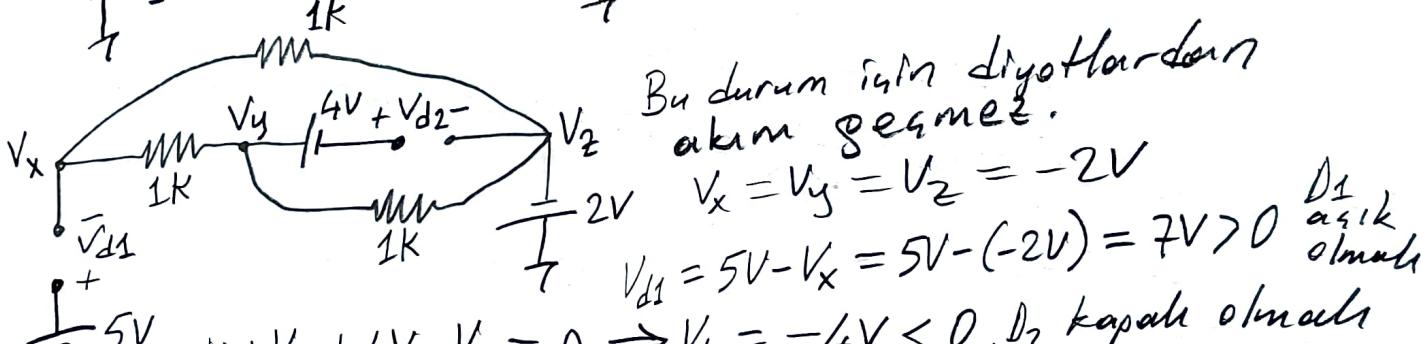
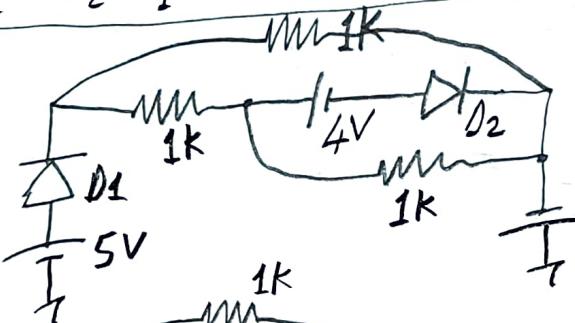
$$R_2 = 2k, R_3 = 3k$$

Diyotlar idealdir.

Once diyotları kapatı farz edip diyotların durumunu incele. Sonra yeni duruma göre diyotları incele ve $V_o = ?$



Diyotlar idealdir.
Since diyotları kapaklı farz edip durumlarını incele.
 $i_{d1} = ?$ $V_{d1} = ?$ $i_{d2} = ?$ $V_{d2} = ?$



$$i_{d1} = i_1 + i_2 = 7mA + 3.5mA = 10.5mA > 0$$

$$V_{d1} = 0V, V_x = 5V - 1k \times i_2 = 5V - 1k \times 3.5mA = 1.5V$$

$$V_{d2} = V_x - 4V - (-2V) = 1.5V - 4V + 2V = -0.5V < 0$$

$$i_{d2} = 0$$

Transistörler

(45)

1904 yılında vakum diyot J.A. Fleming tarafından bulundu. 1906 yılında Lee De Forest, kontrol 12 гараси denen ve ilk yükseltse sayıları triyotun ortaya çıkmamasını sağlayan üçüncü bir bacaklı vakum diyota ekledi.

1947 yılında üç bacaklı yarı iletken bir elektronik olan ilk transistör bulundu. Vakum tüplerle göre avantajı çok fazlaydı. Isıtıcı ve ısınma süresine gereksinimi yoktu. Daha az güç harciyordu. Daha küçük, daha hafif ve daha verimliydi. Daha düşük bir çalışma gerilimine ihtiyaç duyuyordu. Sağlam bir yapıya sahipti.

Transistör üç bacaklı bir elektronik devre元件 oluşturulan küçük AC sinyalini (Akım veya Gerilim) kıvılcımlamak veya anahtarlama (Açma veya Kapatma) yapmak için kullanılır. Transistörün görevini yerine getirebilmesi için önce salışır hale getirilmesi gereklidir.

Transistörün salışması işin hem direk hem de ters polarlarını (kutuplama - öngerilimleme) olmak üzere ikisi beraber yapılır. Öngerilimleme sabit bir akımı transistör üzerinden geçirerek ve transistör üzerinde sabit bir gerilim düşmesi sağlamak işi olduğundan static bir işlemidir.

Transistörün dörtgen salışabildiği noktaların salışma noktaları, bu noktaların oluşturduğu bölgeye ise salışma bölgesi denir. Transistörün salışma noktasına getirmek demek transistör açık hale getirmek demektir.

1900

Vakum
Tüpler

1947

A timeline diagram illustrating the progression of electronic components over time. A horizontal arrow at the bottom is labeled with the letter 'T' at its right end. Above the arrow, there are two vertical lines representing time points. The left vertical line is associated with the year 1900 and the label 'Vakum Tüpler' (Vacuum Tubes). The right vertical line is associated with the year 1947 and shows two arrows pointing towards it. The top arrow points to the text 'BJT (Bipolar Junction Transistor)', and the bottom arrow points to the text 'FET (Field Effect Transistor)'.

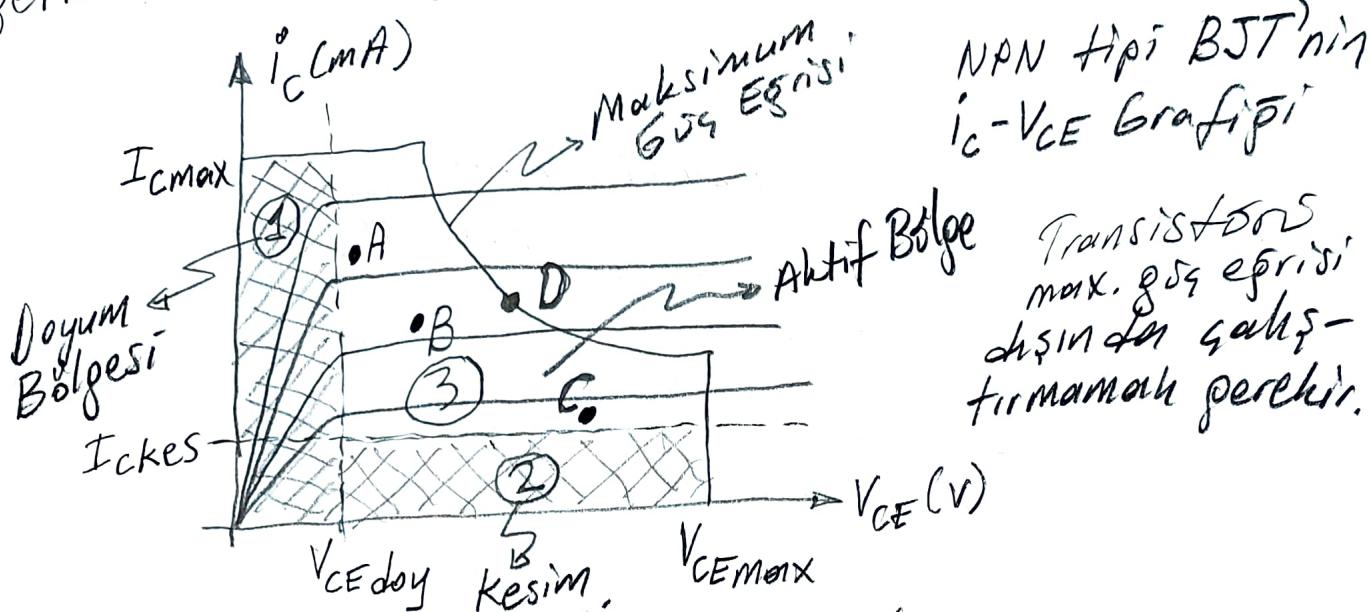
BJT (Bipolar Junction Transistor)
FET (Field Effect Transistor)

Hasan Temurkoç

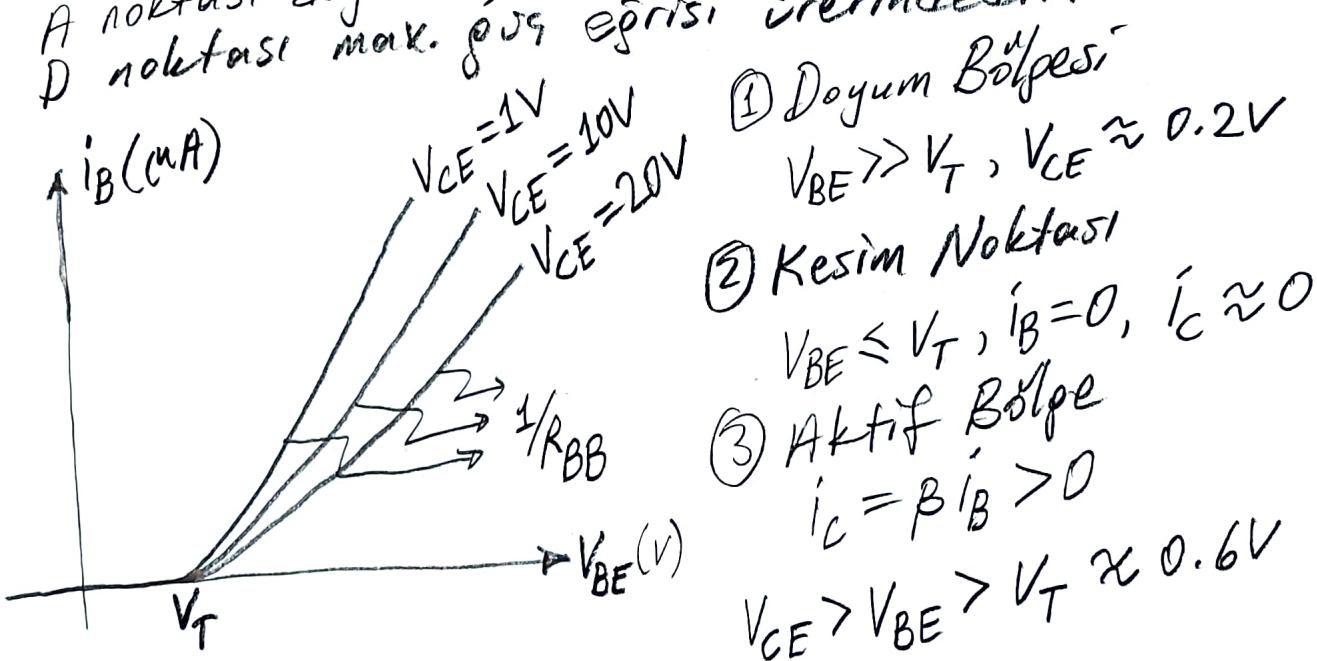
BJT (Güç Kutuplu Yüzey Birleşmeli Transistor)

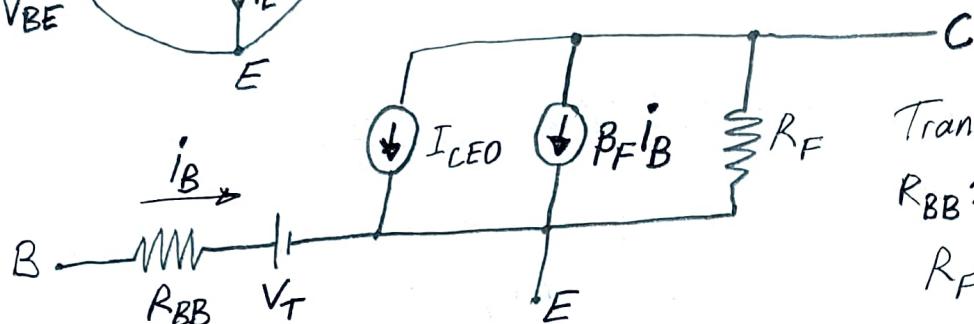
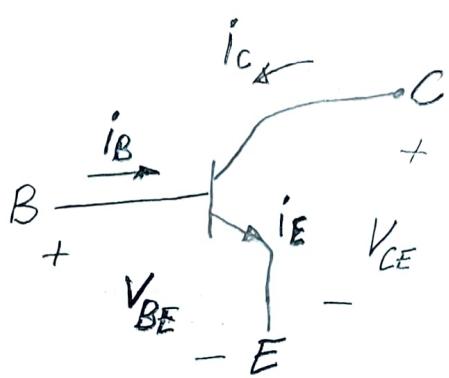
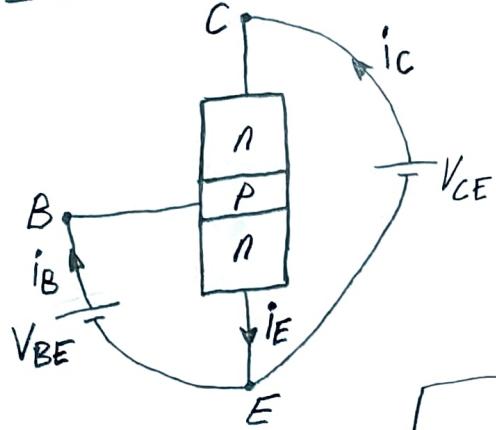
(46)

Bipolar Junction Transistor (BJT)'ler hem elektron hem de oyuk akımının kullanılduğu çift kutuplu akım kontrollü transistörlerdir. NPN ve PNP olmak üzere iki tipte üretilirler. Aralarındaki tek fark, kutuplama yönlerinin birbirine zıt olmasıdır. P'den N'ye düz kutuplaması, N'den P'ye ters kutuplama yapılır. BJT'ler uygun kutuplandıklarında görevlerini yerine getirirler. Kutuplaması transistörün açık durumunu getirmek ve en doğrusal bölgede çalışmasını sağlamak için yapılır.



B noktası tam ortada olduğundan en uygun çalışma noktasıdır.
 A noktası doyuma, C noktası kesime yakındır.
 D noktası mark. eşrişi üzerindedir.



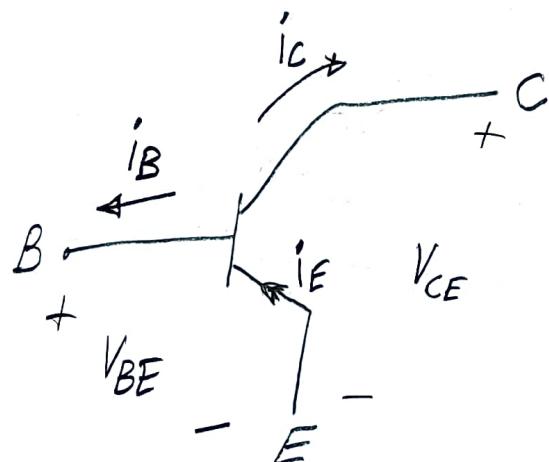
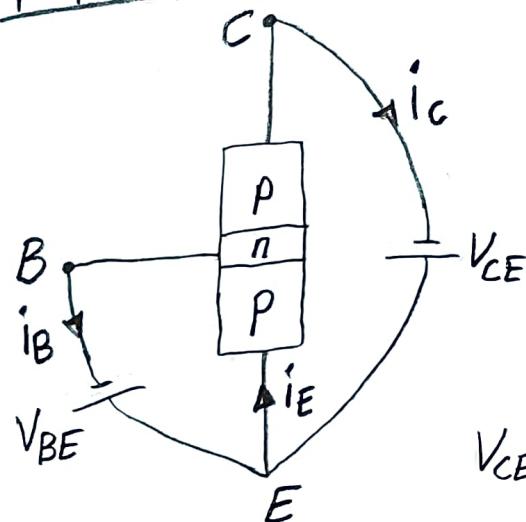
n-p-n tipi BJT

Transistor ideal ise
 $R_{BB} \approx 0$, $I_{CEO} \approx 0$
 $R_F \rightarrow \infty$ olur.

Bu durumda $\beta_F = \beta$, $V_T = 0.6V$ alınır.

$$V_{CE} > V_{BE} \geq V_T \approx 0.6V$$

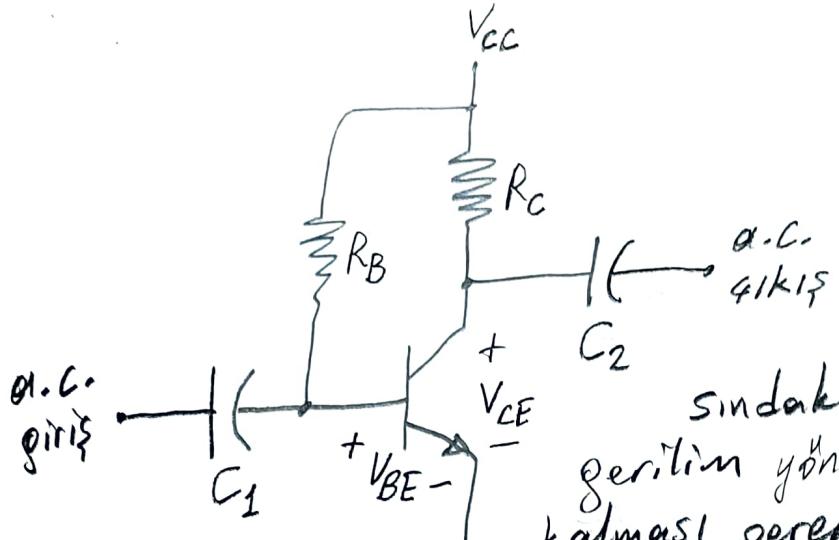
$$\begin{aligned} i_C &= \beta i_B = \alpha i_E & \alpha = \frac{\beta}{\beta+1}, \quad \beta = \frac{\alpha}{1-\alpha} \\ i_E &= (\beta+1)i_B & \beta \gg 1 \text{ ise } \alpha \approx 1 \text{ alınır.} \end{aligned}$$

p-n-p tipi BJT

$$V_{CE} < V_{BE} < -V_T \approx -0.6V$$

$$i_C = \beta i_B$$

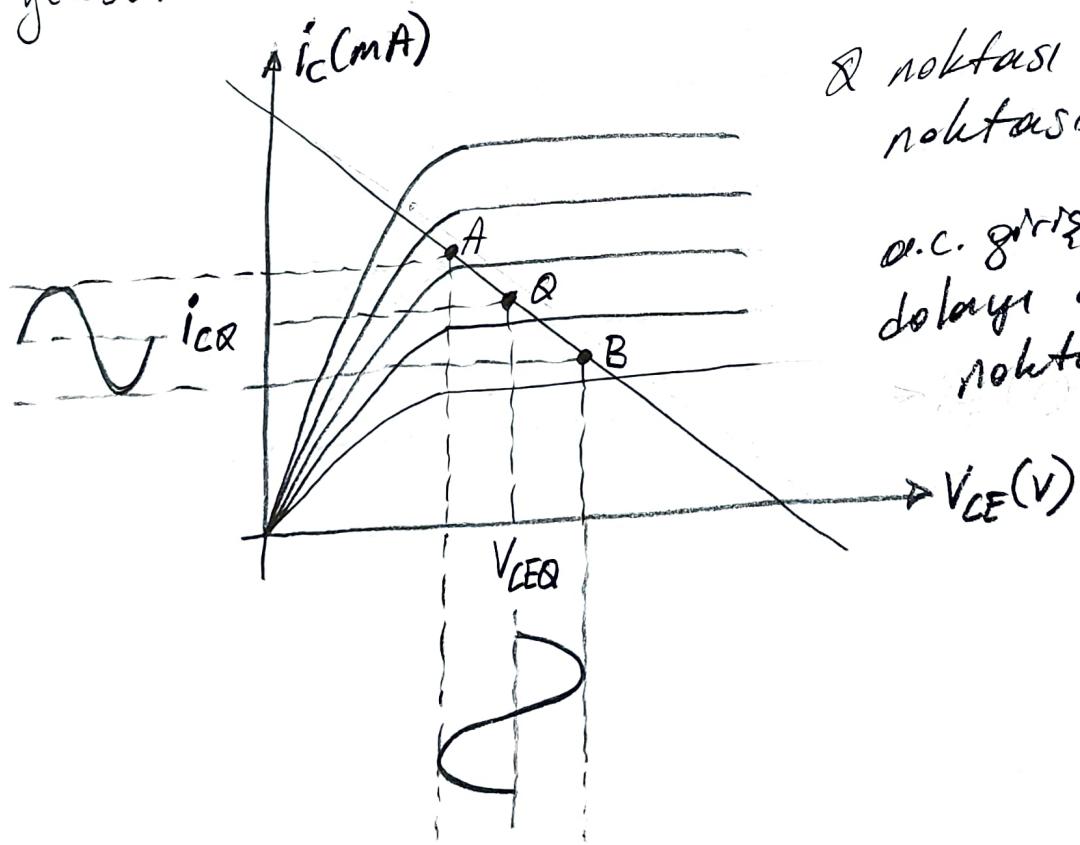
$$i_E = i_C + i_B = (\beta + 1)i_B$$



Kutuplamaya ek olarak devreye bir sinyal bağlandığında çalışma noktası kayar. Çalışma noktası

α -C. gikisi C_2 arasıdır. Sindaki kaymaların akım ve gerilim yönünden makul sınırlarda kalması gereklidir ki transistor doğru çalışabilse.

DC kutuplamada kondansatörler dolup filtreleme görevi yapar. AC giriş sinyalinin frekansı yükselse olduğundan kondansatörleri doldurup boşaltamaz. Kondansatörler DC işin kapaklı, AC işin asıktır. V_{CC} devreyi salıtır duruma getirir. Gikisə DC yansımaz. AC sinyali yükseltilmiş olarak gikisə yansır.



Q noktası çalışma noktasıdır.

AC giriş sinyalinden dolayı çalışma noktası kayar.